

TL08xx FET 入力オペアンプ

1 特長

- 高いスルーレート: 20V/μs (TL08xH、代表値)
- 低いオフセット電圧: 1mV (TL08xH、代表値)
- 低いオフセット電圧ドリフト: 2μV/°C
- 低消費電力: 940μA/ch (TL08xH、代表値)
- 広い同相範囲と差動電圧範囲
 - 同相入力電圧範囲に V_{CC+} を含む
- 低い入力バイアスとオフセット電流
- 低ノイズ:
 $f = 1\text{kHz}$ で $V_n = 18\text{nV}/\sqrt{\text{Hz}}$ (代表値)
- 出力短絡保護
- 低い全高調波歪み: 0.003% (標準値)
- 広い電源電圧範囲:
 $\pm 2.25\text{V} \sim \pm 20\text{V}$ 、4.5V ~ 40V

2 アプリケーション

- ソーラー エネルギー: スtring および 中央インバータ
- モーター ドライブ: AC および サーボ ドライブ 制御 と 出力 段 モジュール
- 単相 オンライン UPS
- 3 相 UPS
- プロ オーディオ ミキサ
- バッテリ テスト 機器

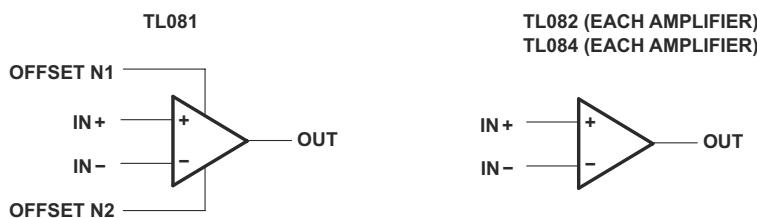
3 概要

TL08xH (TL081H、TL082H、TL084H) ファミリのデバイスは、業界標準の TL08x (TL081、TL082、TL084) デバイスの次世代バージョンです。これらのデバイスは、低オフセット (1mV、代表値)、高スルーレート (20V/μs)、正電源への同相入力などの特長を備え、コスト重視のアプリケーション向けに最適です。高 ESD (1.5kV、HBM)、EMI および RF フィルタの内蔵、 $-40^{\circ}\text{C} \sim 125^{\circ}\text{C}$ の温度範囲での動作により、TL08xH デバイスは最も過酷で要求の厳しいアプリケーションで使用できます。

製品情報

部品番号	パッケージ (1)	本体サイズ (公称)(2)
TL081x	P (PDIP, 8)	9.59mm × 6.35mm
	DCK (SC70, 5)	2mm × 1.25mm
	PS (SO, 8)	6.2mm × 5.3mm
	D (SOIC, 8)	4.9mm × 3.9mm
	DBV (SOT-23, 5)	2.9mm × 1.6mm
TL082x	P (PDIP, 8)	9.59mm × 6.35mm
	PS (SO, 8)	6.2mm × 5.3mm
	D (SOIC, 8)	4.9mm × 3.9mm
	DDF (SOT-23, 8)	2.9mm × 1.6mm
	PW (TSSOP, 8)	4.4mm × 3mm
TL082M	JG (CDIP, 8)	9.6mm × 6.67mm
	FK (LCCC, 20)	8.89mm × 8.89mm
TL084x	N (PDIP, 14)	19.3mm × 6.35mm
	NS (SO, 14)	10.3mm × 5.3mm
	D (SOIC, 14)	8.65mm × 3.91mm
	DYY (SOT-23, 14)	4.2mm × 2mm
	PW (TSSOP, 14)	5mm × 4.4mm
TL084M	J (CDIP, 14)	19.56mm × 6.67mm
	FK (LCCC, 20)	8.89mm × 8.89mm

- (1) 詳細については、[セクション 11](#) を参照してください。
 (2) 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。



ロジック シンボル

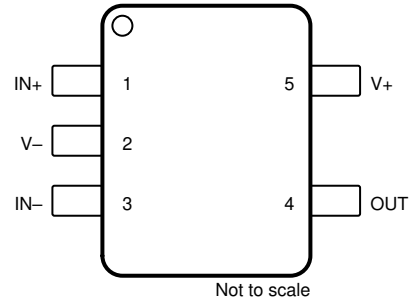
Table of Contents

1 特長	1	7.1 Overview.....	25
2 アプリケーション	1	7.2 Functional Block Diagram.....	25
3 概要	1	7.3 Feature Description.....	25
4 Pin Configuration and Functions	3	7.4 Device Functional Modes.....	25
5 Specifications	9	8 Applications and Implementation	26
5.1 Absolute Maximum Ratings.....	9	8.1 Application Information.....	26
5.2 ESD Ratings.....	9	8.2 Typical Applications.....	26
5.3 Recommended Operating Conditions.....	9	8.3 System Examples.....	27
5.4 Thermal Information for Single Channel.....	10	8.4 Power Supply Recommendations.....	28
5.5 Thermal Information for Dual Channel.....	10	8.5 Layout.....	28
5.6 Thermal Information for Quad Channel.....	11	9 Device and Documentation Support	30
5.7 Electrical Characteristics: TL08xH.....	12	9.1 ドキュメントの更新通知を受け取る方法.....	30
5.8 Electrical Characteristics (DC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM.....	14	9.2 サポート・リソース.....	30
5.9 Electrical Characteristics (AC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM.....	16	9.3 Trademarks.....	30
5.10 Typical Characteristics: TL08xH.....	17	9.4 静電気放電に関する注意事項.....	30
6 Parameter Measurement Information	24	9.5 用語集.....	30
7 Detailed Description	25	10 Revision History	30
		11 Mechanical, Packaging, and Orderable Information	31

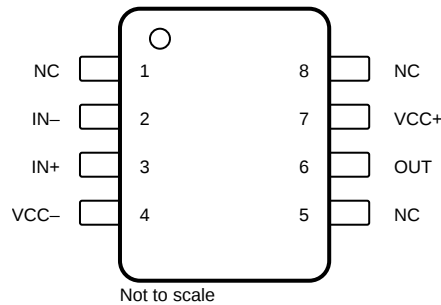
4 Pin Configuration and Functions



**図 4-1. TL081H DBV Package,
5-Pin SOT-23
(Top View)**



**図 4-2. TL081H DCK Package,
5-Pin SC70
(Top View)**



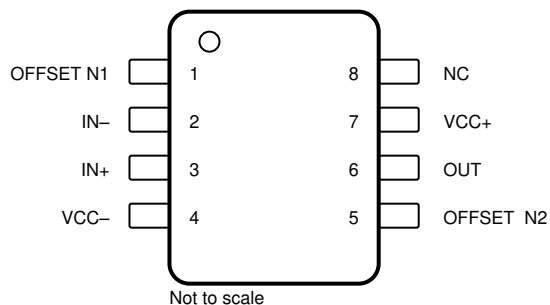
NC- no internal connection

**図 4-3. TL081H D Package,
8-Pin SOIC
(Top View)**

表 4-1. Pin Functions: TL081H

NAME	PIN			TYPE ⁽¹⁾	DESCRIPTION
	DBV	DCK	D		
IN-	4	3	2	I	Inverting input
IN+	3	1	3	I	Noninverting input
NC	—	—	8	—	Do not connect
NC	—	—	1	—	Do not connect
NC	—	—	5	—	Do not connect
OUT	1	4	6	O	Output
VCC-	2	2	4	—	Power supply
VCC+	5	5	7	—	Power supply

(1) I = input, O = output



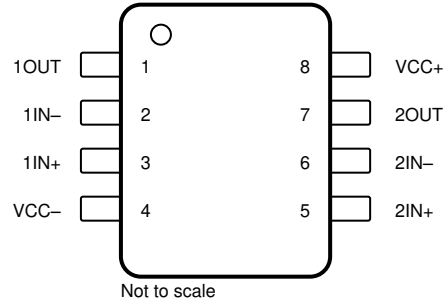
NC- no internal connection

**図 4-4. TL081x D, P, and PS Package,
8-Pin SOIC, PDIP, and SO
(Top View)**

表 4-2. Pin Functions: TL081x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
IN-	2	I	Inverting input
IN+	3	I	Noninverting input
NC	8	—	Do not connect
OFFSET N1	1	—	Input offset adjustment
OFFSET N2	5	—	Input offset adjustment
OUT	6	O	Output
VCC-	4	—	Power supply
VCC+	7	—	Power supply

(1) I = input, O = output

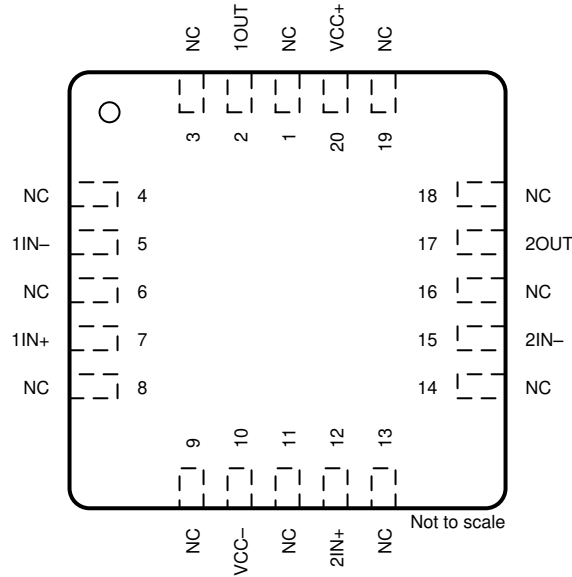


**図 4-5. TL082x D, DDF, DGK, JG, P, PS, and PW Package,
 8-Pin SOIC, SOT-23 (8), VSSOP, CDIP, PDIP, SO, and TSSOP
 (Top View)**

表 4-3. Pin Functions: TL082x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1IN-	2	I	Inverting input
1IN+	3	I	Noninverting input
1OUT	1	O	Output
2IN-	6	I	Inverting input
2IN+	5	I	Noninverting input
2OUT	7	O	Output
VCC-	4	—	Power supply
VCC+	8	—	Power supply

(1) I = input, O = output



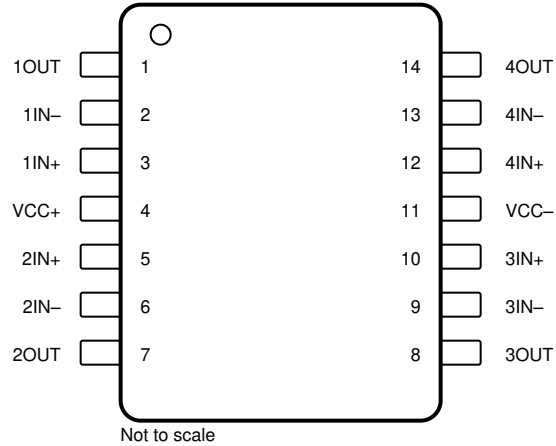
NC- no internal connection

**図 4-6. TL082 FK Package,
20-Pin LCCC
(Top View)**

表 4-4. Pin Functions: TL082x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1IN-	5	I	Inverting input
1IN+	7	I	Noninverting input
1OUT	2	O	Output
2IN-	15	I	Inverting input
2IN+	12	I	Noninverting input
2OUT	17	O	Output
NC	1, 3, 4, 6, 8, 9, 11, 13, 14, 16, 18, 19	—	Do not connect
VCC-	10	—	Power supply
VCC+	20	—	Power supply

(1) I = input, O = output

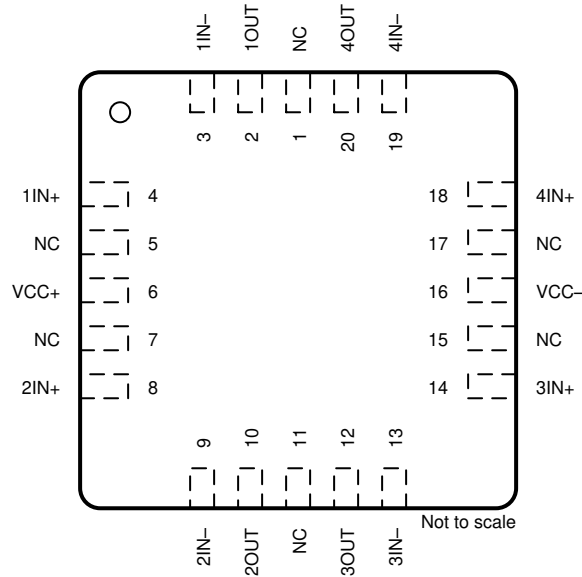


**図 4-7. TL084x D, N, NS, PW, J, and DYY Package,
 14-Pin SOIC, PDIP, SO, TSSOP, CDIP, and SOT-23 (14)
 (Top View)**

表 4-5. Pin Functions: TL084x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1IN-	2	I	Inverting input
1IN+	3	I	Noninverting input
1OUT	1	O	Output
2IN-	6	I	Inverting input
2IN+	5	I	Noninverting input
2OUT	7	O	Output
3IN-	9	I	Inverting input
3IN+	10	I	Noninverting input
3OUT	8	O	Output
4IN-	13	I	Inverting input
4IN+	12	I	Noninverting input
4OUT	14	O	Output
V _{CC-}	11	—	Power supply
V _{CC+}	4	—	Power supply

(1) I = input, O = output



NC- no internal connection

**図 4-8. TL084 FK Package,
20-Pin LCCC
(Top View)**

表 4-6. Pin Functions: TL084x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1IN-	3	I	Inverting input
1IN+	4	I	Noninverting input
1OUT	2	O	Output
2IN-	9	I	Inverting input
2IN+	8	I	Noninverting input
2OUT	10	O	Output
3IN-	13	I	Inverting input
3IN+	14	I	Noninverting input
3OUT	12	O	Output
4IN-	19	I	Inverting input
4IN+	18	I	Noninverting input
4OUT	20	O	Output
NC	1, 5, 7, 11, 15, 17	—	Do not connect
VCC-	16	—	Power supply
VCC+	6	—	Power supply

(1) I = input, O = output

5 Specifications

5.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT
Supply voltage, $V_S = (V+) - (V-)$	All NS and PS packages; All TL08xM devices		-0.3	36	V
	All other devices		0	42	V
Signal input pins	Common-mode voltage ⁽³⁾	All NS and PS packages; All TL08xM devices	$(V-) - 0.3$	$(V-) + 36$	V
		All other devices	$(V-) - 0.5$	$(V+) + 0.5$	V
	Differential voltage ⁽³⁾	All NS and PS packages; All TL08xM devices ⁽⁴⁾	$(V-) - 0.3$	$(V-) + 36$	V
		All other devices		$V_S + 0.2$	V
Current ⁽³⁾	All NS and PS packages; All TL07xM devices		50	mA	
	All other devices		-10	10	mA
Output short-circuit ⁽²⁾			Continuous		
Operating ambient temperature, T_A			-55	150	°C
Junction temperature, T_J				150	°C
Case temperature for 60 seconds - FK package				260	°C
Lead temperature 1.8 mm (1/16 inch) from case for 10 seconds				300	°C
Storage temperature, T_{stg}			-65	150	°C

- Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- Short-circuit to ground, one amplifier per package.
- Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5V beyond the supply rails must be current limited to 10 mA or less.
- Differential voltage only limited by input voltage.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_S	Supply voltage, $(V+) - (V-)$	All NS and PS packages; All TL08xM devices ⁽¹⁾	10	30	V
		All other devices	4.5	40	V
V_I	Input voltage range	All NS and PS packages; All TL08xM devices	$(V-) + 2$	$(V+) + 0.1$	V
		All other devices	$(V-) + 4$	$(V+) + 0.1$	V
T_A	Specified temperature	TL08xM	-55	125	°C
		TL08xH	-40	125	°C
		TL08xI	-40	85	°C
		TL08xC	0	70	°C

- $V+$ and $V-$ are not required to be of equal magnitude, provided that the total V_S ($V+ - V-$) is between 10V and 30V.

5.4 Thermal Information for Single Channel

THERMAL METRIC ⁽¹⁾		TL081xx					UNIT
		D (SOIC)	DCK (SC70)	DBV (SOT-23)	P (PDIP)	PS (SO)	
		8 PINS	5 PINS	5 PINS	8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	158.8	217.5	212.2	85	95	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	98.6	113.1	111.1	–	–	°C/W
R _{θJB}	Junction-to-board thermal resistance	102.3	63.8	79.4	–	–	°C/W
ψ _{JT}	Junction-to-top characterization parameter	45.8	34.8	51.8	–	–	°C/W
ψ _{JB}	Junction-to-board characterization parameter	101.5	63.5	79.0	–	–	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.5 Thermal Information for Dual Channel

THERMAL METRIC ⁽¹⁾		TL082xx								UNIT
		D (SOIC)	DDF (SOT-23)	FK (LCCC)	JG (CDIP)	P (PDIP)	PS (SO)	PW (TSSOP)	U (CFP)	
		8 PINS	8 PINS	20 PINS	8 PINS	8 PINS	8 PINS	8 PINS	10 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	147.8	181.5	–	–	85	95	200.3	169.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	88.2	112.5	5.61	15.05	–	–	89.4	62.1	°C/W
R _{θJB}	Junction-to-board thermal resistance	91.4	98.2	–	–	–	–	131.0	176.2	°C/W
ψ _{JT}	Junction-to-top characterization parameter	36.8	17.2	–	–	–	–	22.2	48.4	°C/W
ψ _{JB}	Junction-to-board characterization parameter	90.6	97.6	–	–	–	–	129.3	144.1	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	–	–	–	–	N/A	5.4	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.6 Thermal Information for Quad Channel

THERMAL METRIC ⁽¹⁾		TL084xx								UNIT
		D (SOIC)	DYY (SOT-23)	FK (TSSOP)	J (TSSOP)	N (TSSOP)	NS (TSSOP)	PW (TSSOP)	W (TSSOP)	
		14 PINS	14 PINS	20 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	114.2	153.2	–	–	80	76	–	128.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	70.3	88.7	5.61	14.5	–	–	14.5	56.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	70.2	65.4	–	–	–	–	–	127.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	28.8	9.5	–	–	–	–	–	29	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	69.8	65.0	–	–	–	–	–	106.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	–	–	–	–	–	0.5	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.7 Electrical Characteristics: TL08xH

For $V_S = (V_{CC+}) - (V_{CC-}) = 4.5V$ to $40V$ ($\pm 2.25V$ to $\pm 20V$) at $T_A = 25^\circ C$, $R_L = 10k\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_O = V_S / 2$, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V_{OS}	Input offset voltage				± 1	± 4	mV
				$T_A = -40^\circ C$ to $125^\circ C$		± 5	
dV_{OS}/dT	Input offset voltage drift			$T_A = -40^\circ C$ to $125^\circ C$	± 2		$\mu V/^\circ C$
PSRR	Input offset voltage versus power supply	$V_S = 5V$ to $40V$, $V_{CM} = V_S / 2$	$T_A = -40^\circ C$ to $125^\circ C$		± 1	± 10	$\mu V/V$
	Channel separation			$f = 0Hz$		10	
INPUT BIAS CURRENT							
I_B	Input bias current				± 1	± 120	pA
				DCK and DBV packages	± 1	± 300	pA
				$T_A = -40^\circ C$ to $125^\circ C$ (1)			± 5
I_{OS}	Input offset current				± 0.5	± 120	pA
				DCK and DBV packages	± 0.5	± 250	pA
				$T_A = -40^\circ C$ to $125^\circ C$ (1)			± 5
NOISE							
E_N	Input voltage noise	$f = 0.1Hz$ to $10Hz$			9.2		μV_{PP}
						1.4	μV_{RMS}
e_N	Input voltage noise density	$f = 1kHz$			37		nV/ \sqrt{Hz}
		$f = 10kHz$			21		
i_N	Input current noise	$f = 1kHz$			80		fA/ \sqrt{Hz}
INPUT VOLTAGE RANGE							
V_{CM}	Common-mode voltage range			$(V_{CC-}) + 1.5$		(V_{CC+})	V
CMRR	Common-mode rejection ratio	$V_S = 40V$, $(V_{CC-}) + 2.5V < V_{CM} < (V_{CC+}) - 1.5V$			100	105	dB
					$T_A = -40^\circ C$ to $125^\circ C$		
		$V_S = 40V$, $(V_{CC-}) + 2.5V < V_{CM} < (V_{CC+})$			90	105	dB
					$T_A = -40^\circ C$ to $125^\circ C$		
INPUT CAPACITANCE							
Z_{ID}	Differential				$100 \parallel 2$		M $\Omega \parallel pF$
Z_{ICM}	Common-mode				$6 \parallel 1$		T $\Omega \parallel pF$
OPEN-LOOP GAIN							
A_{OL}	Open-loop voltage gain	$V_S = 40V$, $V_{CM} = V_S / 2$, $(V_{CC-}) + 0.3V < V_O < (V_{CC+}) - 0.3V$	$T_A = -40^\circ C$ to $125^\circ C$	118	125		dB
A_{OL}	Open-loop voltage gain	$V_S = 40V$, $V_{CM} = V_S / 2$, $R_L = 2k\Omega$, $(V_{CC-}) + 1.2V < V_O < (V_{CC+}) - 1.2V$	$T_A = -40^\circ C$ to $125^\circ C$	115	120		dB
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product				5.25		MHz
SR	Slew rate	$V_S = 40V$, $G = +1$, $C_L = 20pF$			20		V/ μs
t_s	Settling time	T_O 0.1%, $V_S = 40V$, $V_{STEP} = 10V$, $G = +1$, $C_L = 20pF$			0.63		μs
		T_O 0.1%, $V_S = 40V$, $V_{STEP} = 2V$, $G = +1$, $C_L = 20pF$			0.56		
		T_O 0.01%, $V_S = 40V$, $V_{STEP} = 10V$, $G = +1$, $C_L = 20pF$			0.91		
		T_O 0.01%, $V_S = 40V$, $V_{STEP} = 2V$, $G = +1$, $C_L = 20pF$			0.48		
	Phase margin	$G = +1$, $R_L = 10k\Omega$, $C_L = 20pF$			56		$^\circ$
	Overload recovery time	$V_{IN} \times \text{gain} > V_S$			300		ns
THD+N	Total harmonic distortion + noise	$V_S = 40V$, $V_O = 6V_{RMS}$, $G = +1$, $f = 1kHz$			0.00012		%
EMIRR	EMI rejection ratio	$f = 1GHz$			53		dB

5.7 Electrical Characteristics: TL08xH (続き)

For $V_S = (V_{CC+}) - (V_{CC-}) = 4.5V$ to $40V$ ($\pm 2.25V$ to $\pm 20V$) at $T_A = 25^\circ C$, $R_L = 10k\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{O_{UT}} = V_S / 2$, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
OUTPUT								
	Voltage output swing from rail	Positive rail headroom	$V_S = 40V, R_L = 10k\Omega$		115	210	mV	
			$V_S = 40V, R_L = 2k\Omega$		520	965		
		Negative rail headroom	$V_S = 40V, R_L = 10k\Omega$		105	215		
			$V_S = 40V, R_L = 2k\Omega$		500	1030		
I_{SC}	Short-circuit current			± 26			mA	
C_{LOAD}	Capacitive load drive				300		pF	
Z_O	Open-loop output impedance	$f = 1MHz, I_O = 0A$			125		Ω	
POWER SUPPLY								
I_Q	Quiescent current per amplifier		$T_A = -40^\circ C$ to $125^\circ C$		$I_O = 0A$	937.5	1125	μA
					$I_O = 0A, (TL081H)$	960	1156	
					$I_O = 0A$		1130	
					$I_O = 0A, (TL082H)$		1143	
					$I_O = 0A, (TL071H)$		1160	
	Turn-On Time	At $T_A = 25^\circ C, V_S = 40V, V_S$ ramp rate $> 0.3V/\mu s$			60		μs	

(1) Max I_B and I_{OS} data is specified based on characterization results.

5.8 Electrical Characteristics (DC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM

For $V_S = (V_{CC+}) - (V_{CC-}) = \pm 15V$ at $T_A = 25^\circ C$, unless otherwise noted

PARAMETER		TEST CONDITIONS ^{(1) (2)}		MIN	TYP	MAX	UNIT
V_{OS}	Input offset voltage	$V_O = 0V$ $R_S = 50 \Omega$	TL08xC		3	10	mV
				$T_A = \text{Full range}$		13	
			TL08xAC		3	6	
				$T_A = \text{Full range}$		7.5	
			TL08xBC		2	3	
				$T_A = \text{Full range}$		5	
			TL08xI		3	6	
				$T_A = \text{Full range}$		8	
TL081M, TL082M		3	6				
	$T_A = \text{Full range}$		9				
TL084M		3	9				
	$T_A = \text{Full range}$		15				
dV_{OS}/dT	Input offset voltage drift	$V_O = 0V, R_S = 50 \Omega$	$T_A = \text{Full range}$		± 18		$\mu V/^\circ C$
I_{OS}	Input offset current	$V_O = 0V$	TL08xC		5	100	pA
				$T_A = \text{Full range}$		10	nA
			TL08xAC, TL08xBC, TL08xI		5	100	pA
				$T_A = \text{Full range}$		2	nA
TL08xM		5	100	pA			
	$T_A = \text{Full range}$		20	nA			
I_B	Input bias current	$V_O = 0V$	TL08xC, TL08xAC, TL08xBC, TL08xI		65	200	pA
				$T_A = \text{Full range}$		7	nA
			TL081M, TL082M		65	200	pA
				$T_A = \text{Full range}$		50	nA
			TL084M		65	200	pA
				$T_A = \text{Full range}$		20	nA
V_{CM}	Common-mode voltage range			± 11	-12 to 15		V
V_{OM}	Maximum peak output voltage swing	$R_L = 10k\Omega$	$T_A = \text{Full range}$	± 12	± 13.5	V	
		$R_L \geq 10k\Omega$		± 12			
		$R_L \geq 2k\Omega$		± 10			
A_{OL}	Open-loop voltage gain	$V_O = 0V$	TL08xC		25	200	V/mV
				$T_A = \text{Full range}$		15	
			TL08xAC, TL08xBC, TL08xI		50	200	
				$T_A = \text{Full range}$		25	
TL08xM		35	200				
	$T_A = \text{Full range}$		15				
GBW	Gain-bandwidth product	All NS and PS packages; All TL08xM devices			3	MHz	
		All other devices			5.25		
R_{ID}	Common-mode input resistance				1	T Ω	
$CMRR$	Common-mode rejection ratio	$V_{IC} = V_{ICR(min)}$ $V_O = 0V$ $R_S = 50 \Omega$	TL08xC		70	100	dB
			TL08xAC, TL08xBC, TL08xI		75	100	
			TL08xM		80	86	
$PSRR$	Input offset voltage versus power supply	$V_S = \pm 9V$ to $\pm 18V$ $V_O = 0V$ $R_S = 50 \Omega$	TL08xC		70	100	dB
			TL08xAC, TL08xBC, TL08xI		80	100	
			TL08xM		80	86	

5.8 Electrical Characteristics (DC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM (続き)

For $V_S = (V_{CC+}) - (V_{CC-}) = \pm 15V$ at $T_A = 25^\circ C$, unless otherwise noted

PARAMETER		TEST CONDITIONS ^{(1) (2)}	MIN	TYP	MAX	UNIT
I_Q	Quiescent current per amplifier	$V_O = 0V$; no load		1.4	2.5	mA
	Channel separation	$f = 0Hz$		1		$\mu V/V$

- (1) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified.
 (2) Full range is $T_A = 0^\circ C$ to $70^\circ C$ for the TL07xC, TL07xAC, and TL07xBC; $T_A = -40^\circ C$ to $85^\circ C$ for the TL07xI; and $T_A = -55^\circ C$ to $125^\circ C$ for the TL07xM.

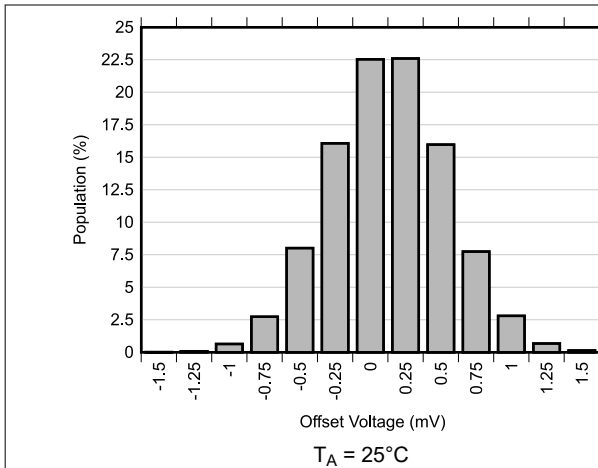
5.9 Electrical Characteristics (AC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM

For $V_S = (V_{CC+}) - (V_{CC-}) = \pm 15V$ at $T_A = 25^\circ C$, unless otherwise noted.

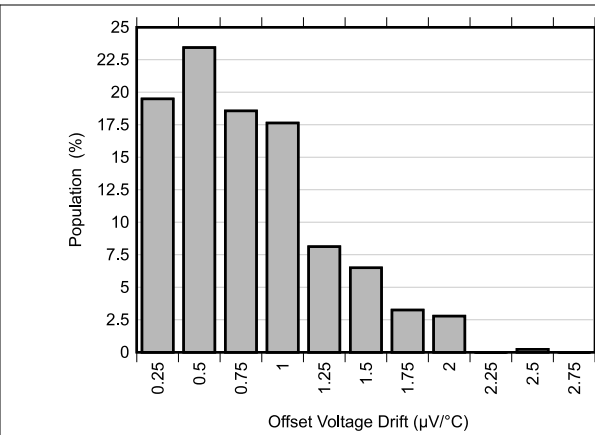
PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
SR	Slew rate	$V_I = 10V, C_L = 100pF, R_L = 2k\Omega$	TL08xM	5	20		V/ μs
			TL08xC, TL08xAC, TL08xBC, TL08xI	8	20		V/ μs
t_S	Settling time	$V_I = 20V, C_L = 100pF, R_L = 2k\Omega$			0.1		μs
					20%		
e_N	Input voltage noise density	All PS and NS packages; All TL08xM devices	$R_S = 20\Omega, f = 1kHz$		18		nV/\sqrt{Hz}
			$f = 1kHz$		37		nV/\sqrt{Hz}
			$f = 10kHz$		21		nV/\sqrt{Hz}
E_N	Input voltage noise	All PS and NS packages; All TL08xM devices	$R_S = 20\Omega, f = 10Hz$ to 10kHz		4		μV_{RMS}
			All other devices	$f = 0.1Hz$ to 10Hz		1.4	
i_N	Input current noise		$R_S = 20\Omega, f = 1kHz$		10		fA/\sqrt{Hz}
	Phase margin	TL08xC, TL08xAC, TL08xBC, TL08xI	$G = +1, R_L = 10k\Omega, C_L = 20pF$		56		°
	Overload recovery time		$V_{IN} \times gain > V_S$		300		ns
THD+N	Total harmonic distortion + noise	All PS and NS packages; All TL08xM devices	$V_O = 6V_{RMS}, R_L \geq 2k\Omega, f = 1kHz, G = +1, R_S \leq 1k\Omega$		0.003		%
			All other devices	$V_S = 40V, V_O = 6V_{RMS}, G = +1, f = 1kHz$		0.00012	
EMIRR	EMI rejection ratio	TL08xC, TL08xAC, TL08xBC, TL08xI	$f = 1GHz$		53		dB
Z_O	Open-loop output impedance	TL07xC, TL07xAC, TL07xBC, TL07xI	$f = 1MHz, I_O = 0A$		125		Ω

5.10 Typical Characteristics: TL08xH

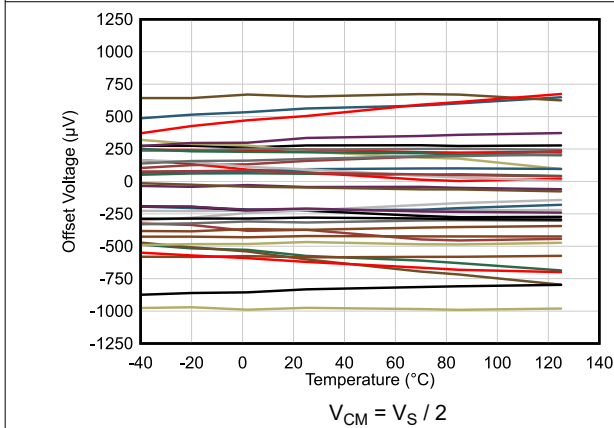
at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)



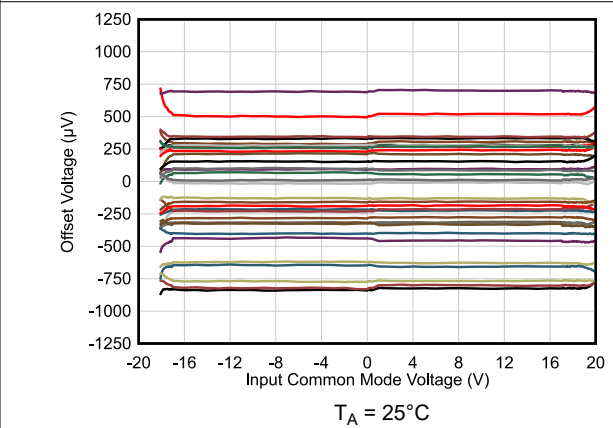
5-1. Offset Voltage Production Distribution



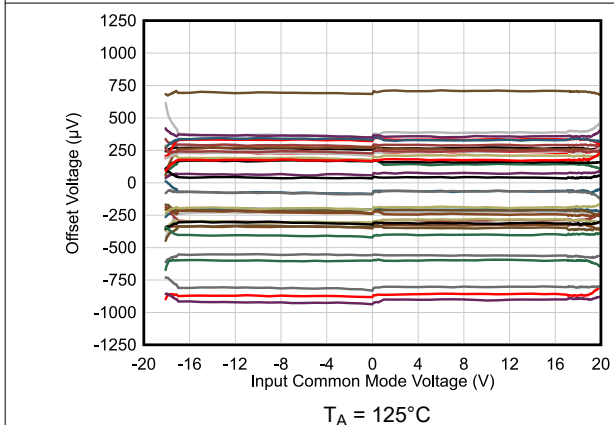
5-2. Offset Voltage Drift Distribution



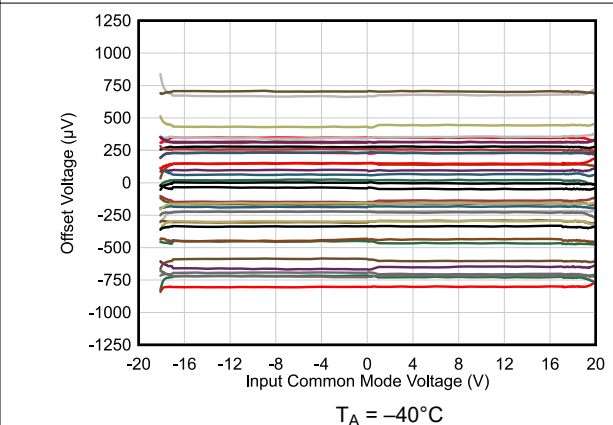
5-3. Offset Voltage vs Temperature



5-4. Offset Voltage vs Common-Mode Voltage



5-5. Offset Voltage vs Common-Mode Voltage



5-6. Offset Voltage vs Common-Mode Voltage

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

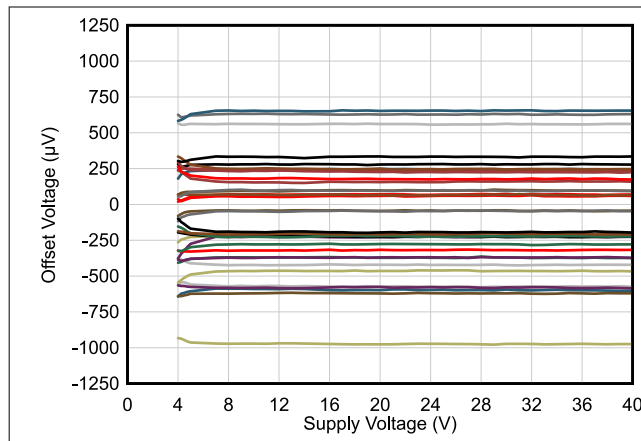


图 5-7. Offset Voltage vs Power Supply

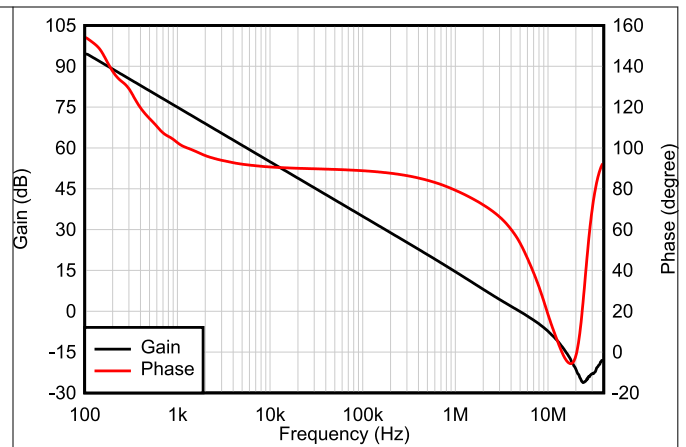


图 5-8. Open-Loop Gain and Phase vs Frequency

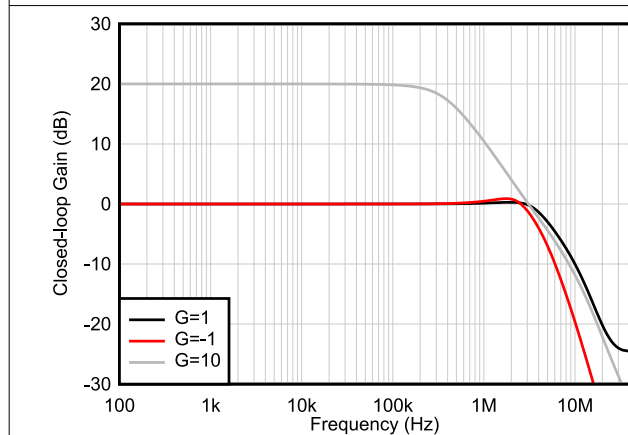


图 5-9. Closed-Loop Gain vs Frequency

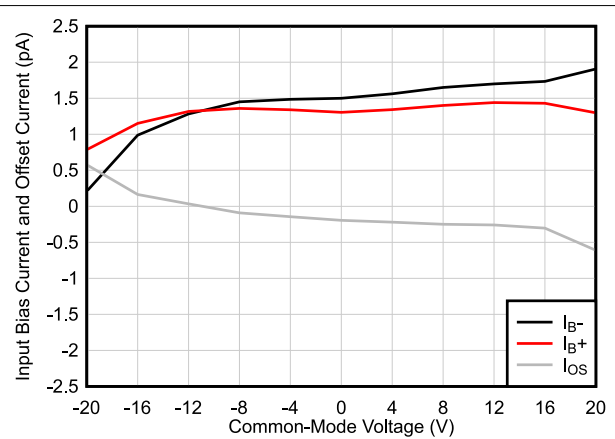


图 5-10. Input Bias Current vs Common-Mode Voltage

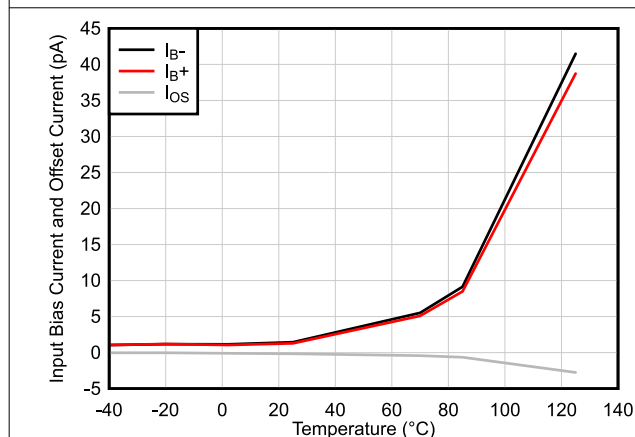


图 5-11. Input Bias Current vs Temperature

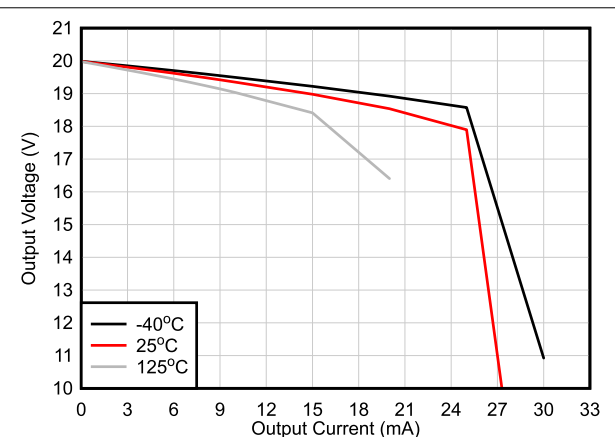
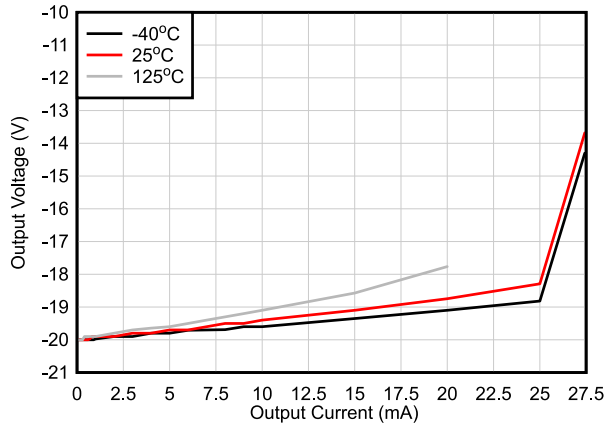


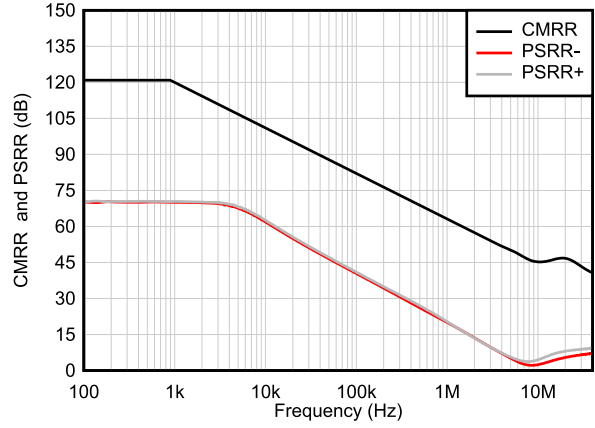
图 5-12. Output Voltage Swing vs Output Current (Sourcing)

5.10 Typical Characteristics: TL08xH (continued)

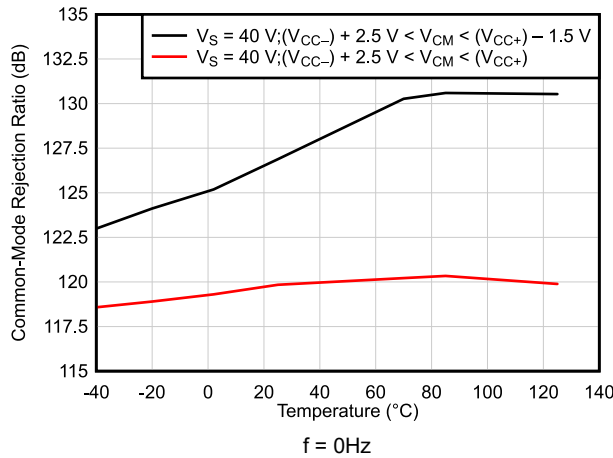
at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)



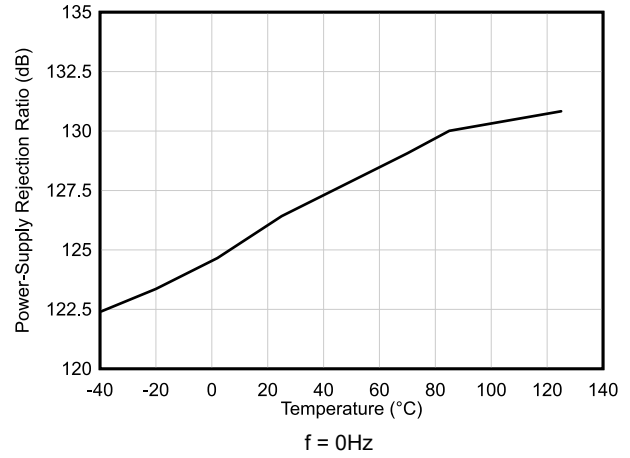
5-13. Output Voltage Swing vs Output Current (Sinking)



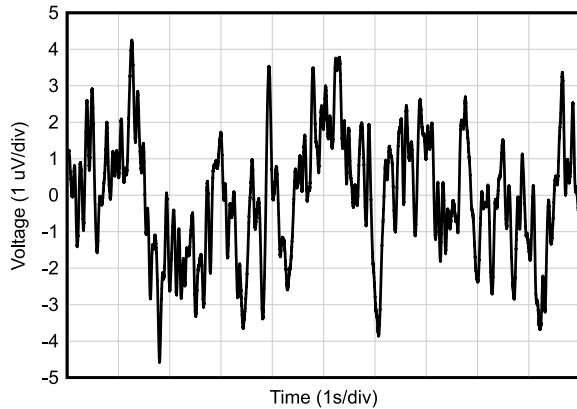
5-14. CMRR and PSRR vs Frequency



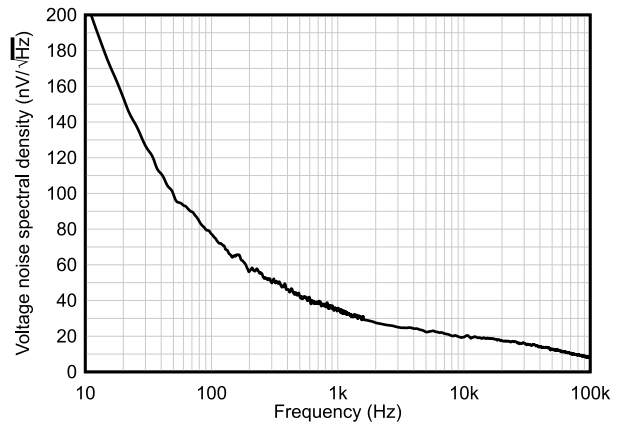
5-15. CMRR vs Temperature (dB)



5-16. PSRR vs Temperature (dB)



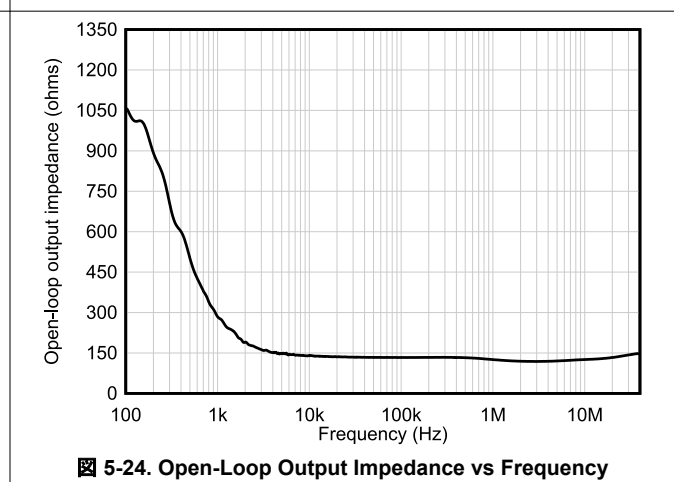
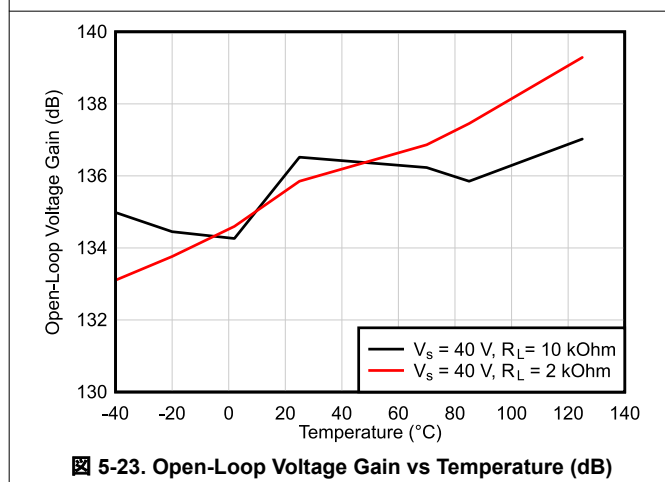
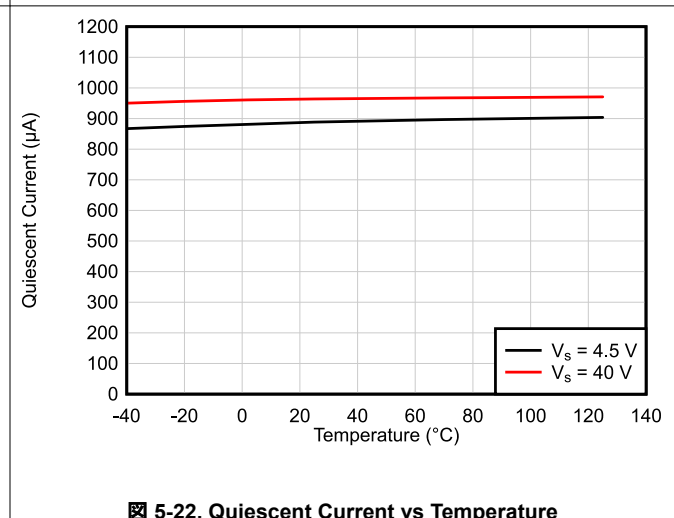
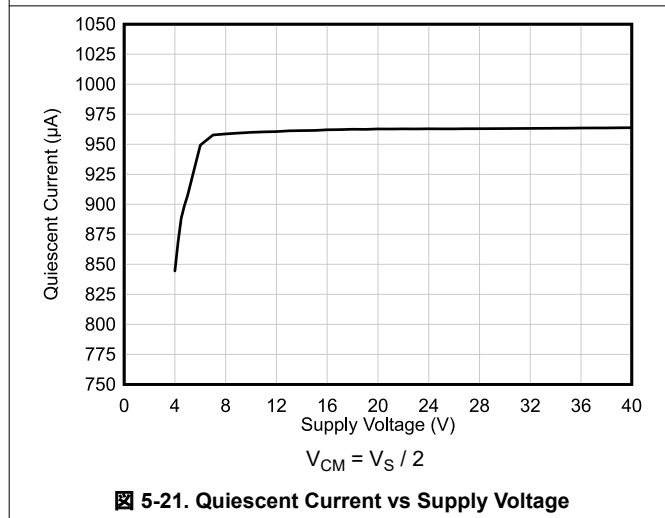
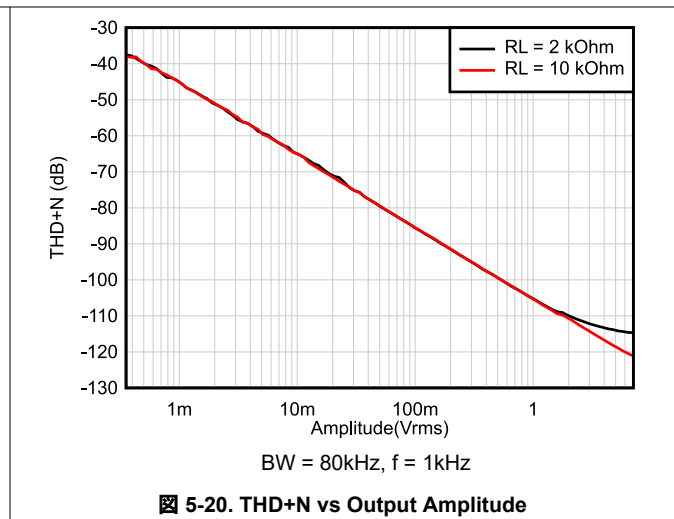
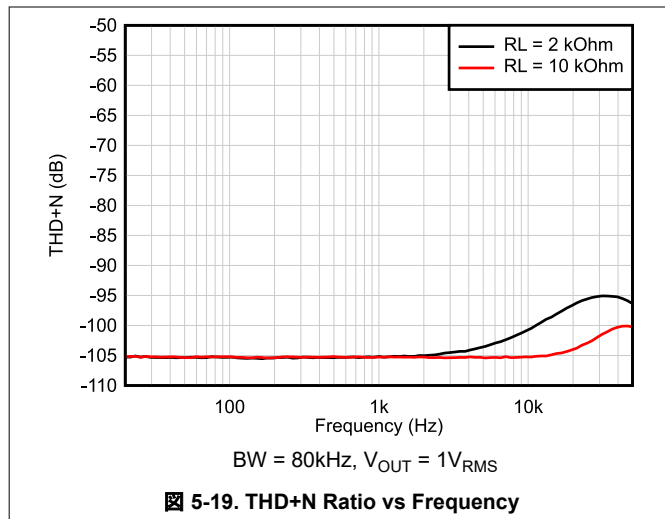
5-17. 0.1-Hz to 10-Hz Noise



5-18. Input Voltage Noise Spectral Density vs Frequency

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)



5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

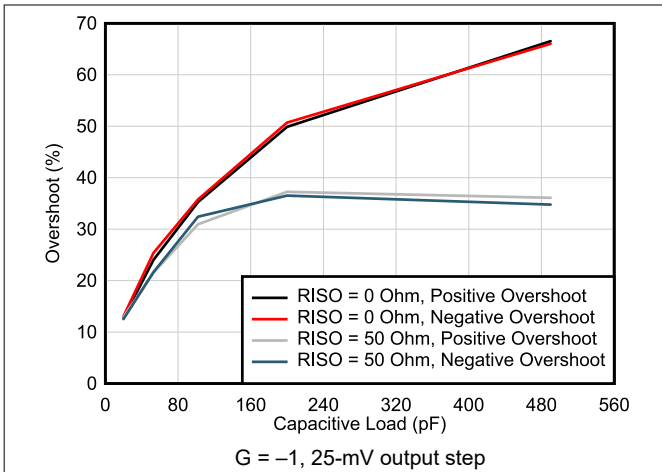


图 5-25. Small-Signal Overshoot vs Capacitive Load

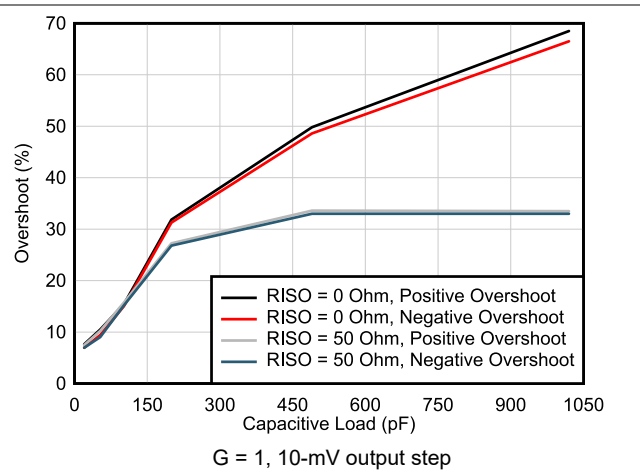
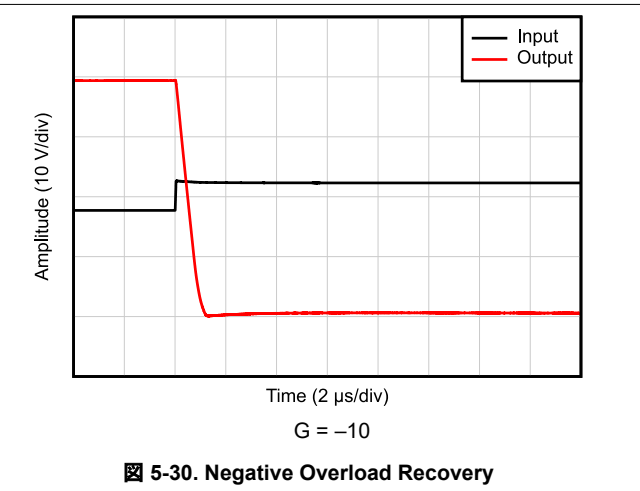
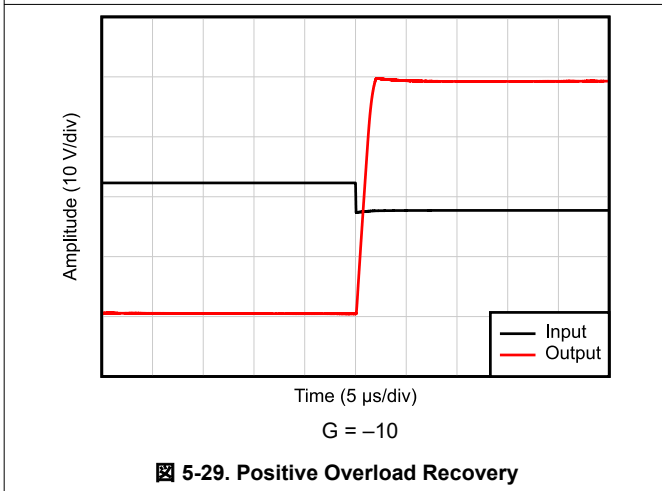
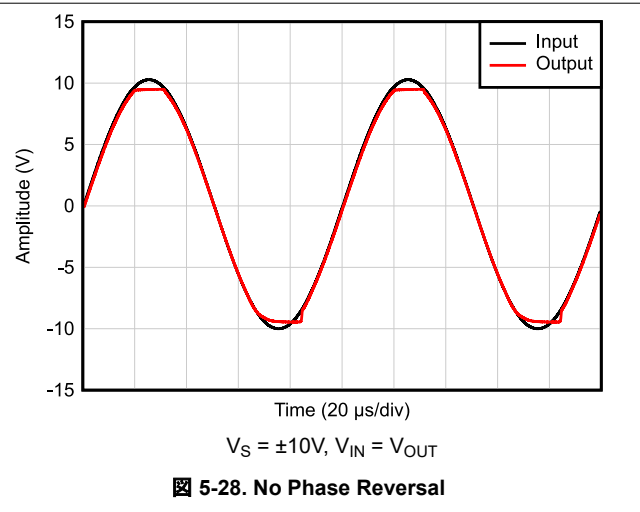
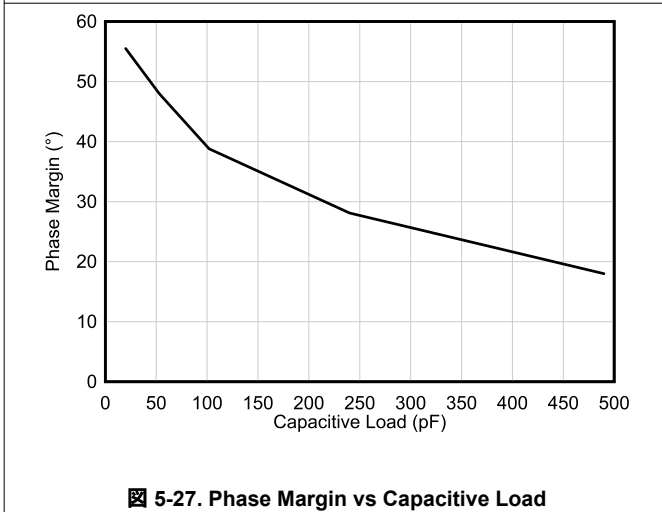
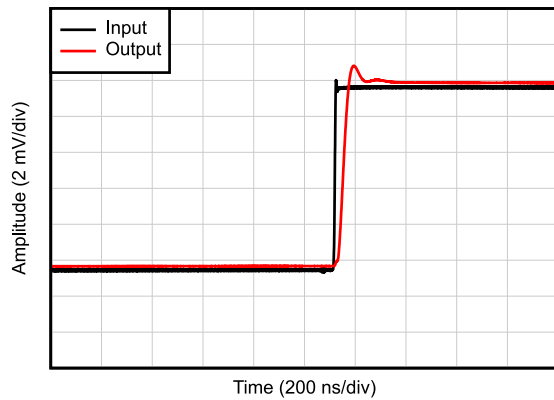


图 5-26. Small-Signal Overshoot vs Capacitive Load

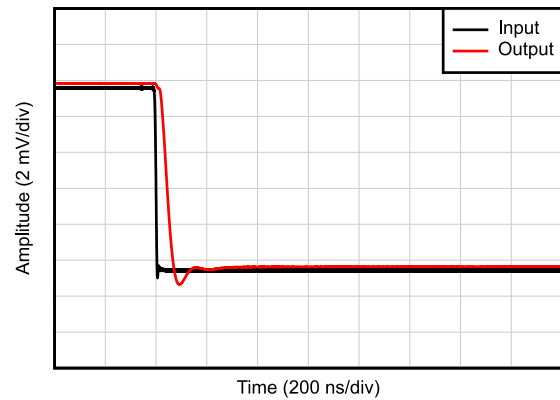


5.10 Typical Characteristics: TL08xH (continued)

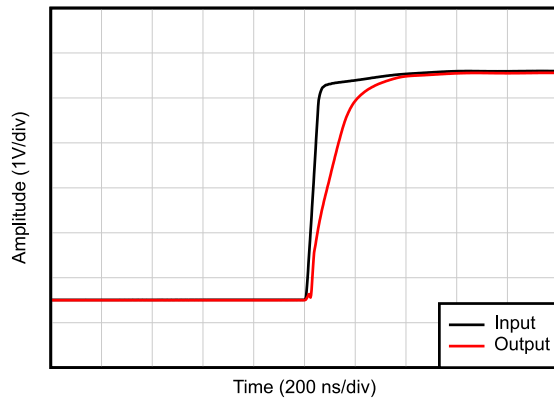
at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)



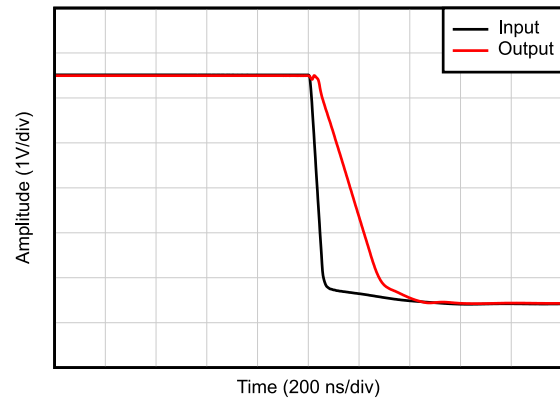
5-31. Small-Signal Step Response, Rising



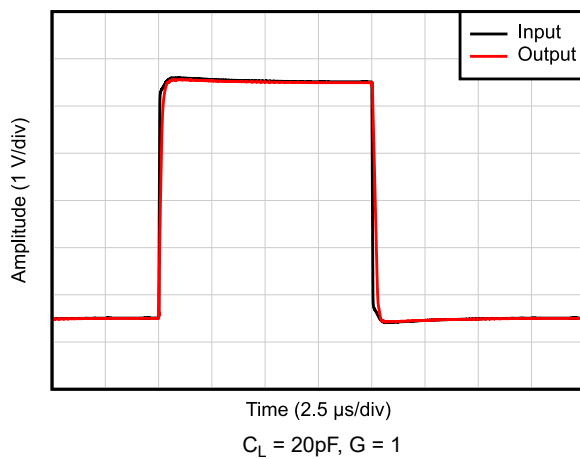
5-32. Small-Signal Step Response, Falling



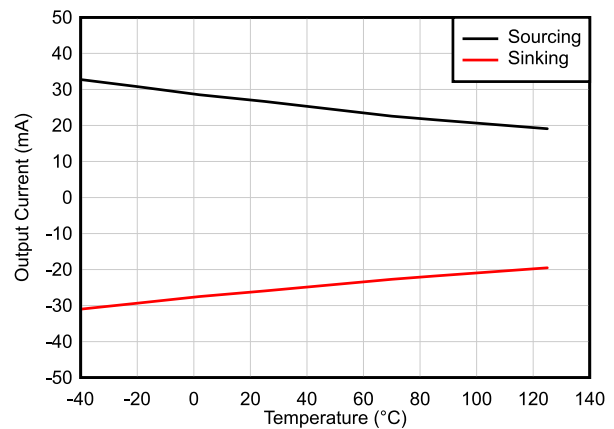
5-33. Large-Signal Step Response (Rising)



5-34. Large-Signal Step Response (Falling)



5-35. Large-Signal Step Response



5-36. Short-Circuit Current vs Temperature

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

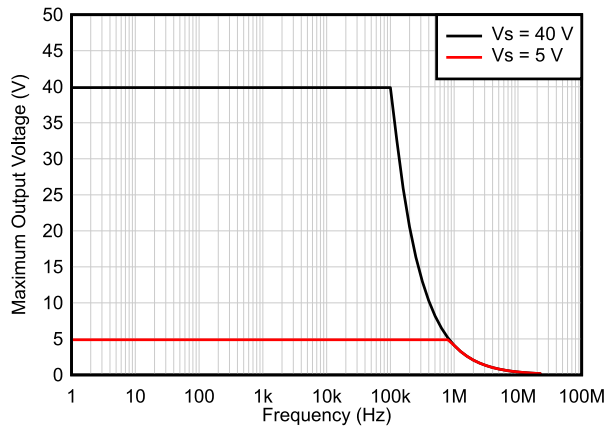


Figure 5-37. Maximum Output Voltage vs Frequency

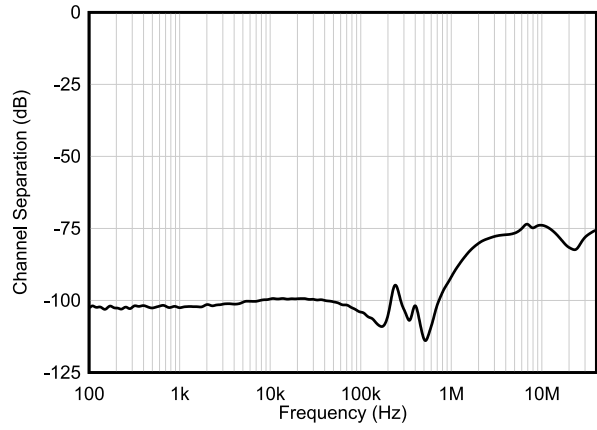


Figure 5-38. Channel Separation vs Frequency

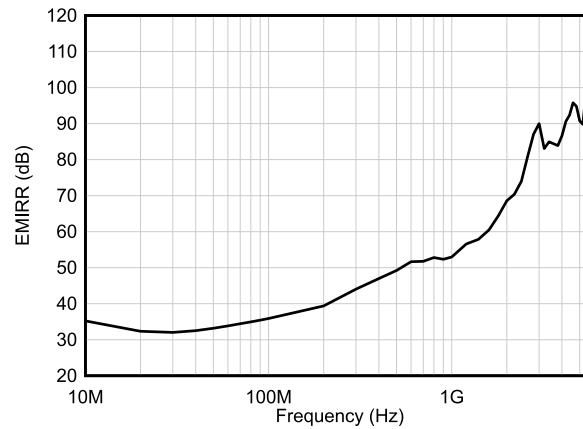


Figure 5-39. EMIRR (Electromagnetic Interference Rejection Ratio) vs Frequency

6 Parameter Measurement Information

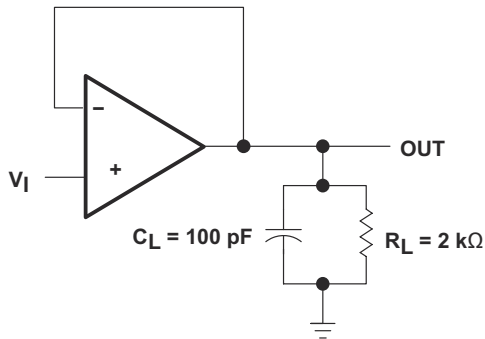


図 6-1. Test Figure 1

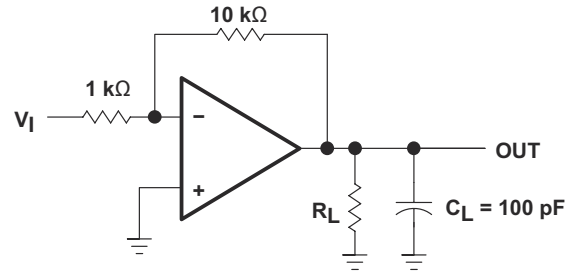


図 6-2. Test Figure 2

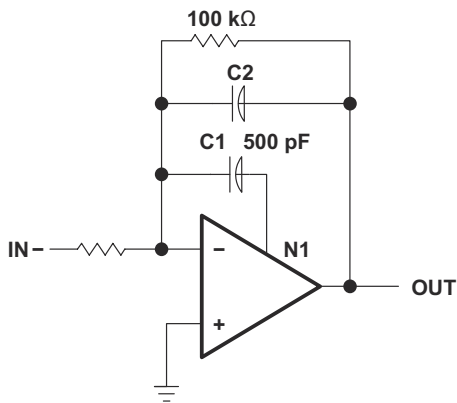


図 6-3. Test Figure 3

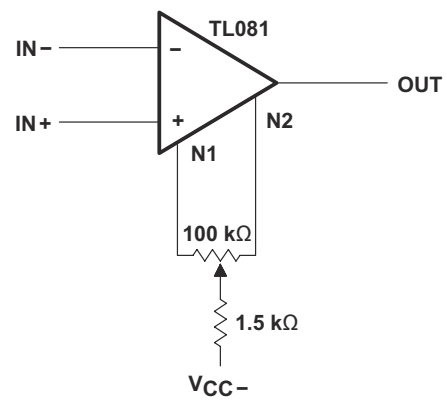


図 6-4. Test Figure 4

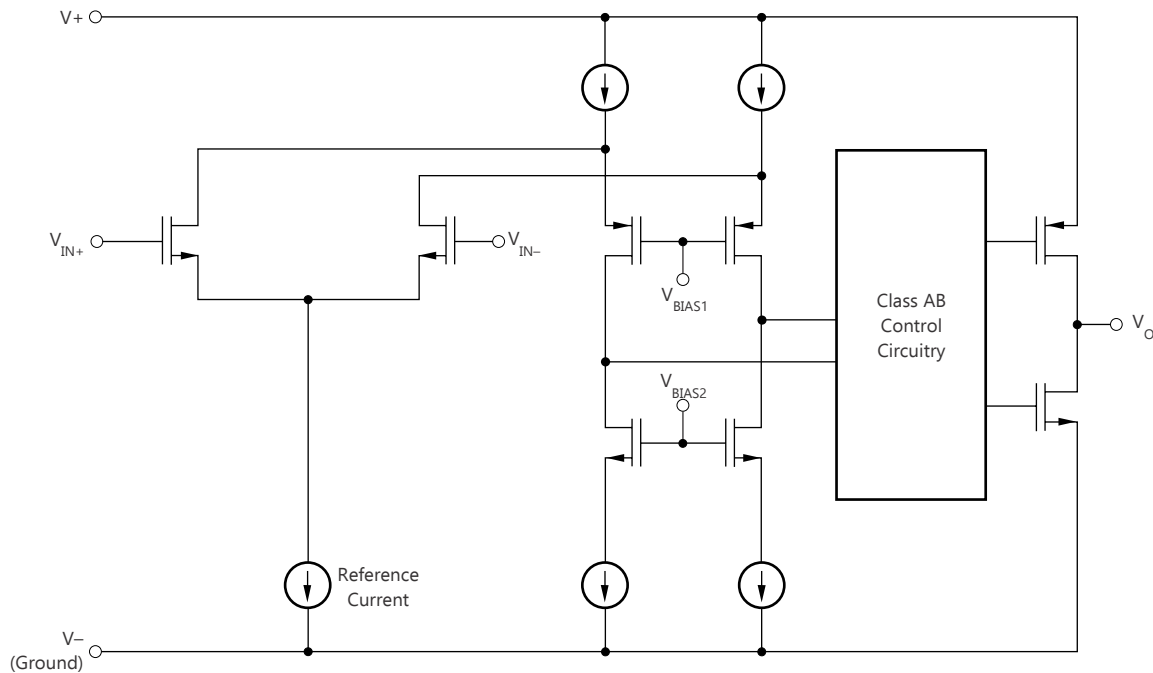
7 Detailed Description

7.1 Overview

The TL08xH family (TL081H, TL082H, and TL084H) is the next-generation family of the industry standard TL08x (TL081, TL082, and TL084) high-voltage general purpose amplifiers. These devices provide outstanding value for cost-sensitive applications requiring high slew rate with high voltage signals, such as motor drive and inverter systems.

A robust MUX-friendly input stage enhances flexibility in design, with common-mode voltage range extending to the positive rail as well as improved settling time in multi-channel applications. Low offset voltage (1mV, typ) and low offset voltage drift ($2\mu\text{V}/^\circ\text{C}$) allows the TL08xH family to be used in rugged applications requiring precision current and voltage sensing. High voltage operation (up to 40V) and high slew rate ($20\text{V}/\mu\text{s}$) make the TL08xH family a premier choice for high-voltage applications with fast transients.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Total Harmonic Distortion

Harmonic distortions to an audio signal are created by electronic components in a circuit. Total harmonic distortion (THD) is a measure of harmonic distortions accumulated by a signal in an audio system. These devices have a very low THD of 0.003% meaning that the TL08x devices will add little harmonic distortion when used in audio signal applications.

7.3.2 Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. These devices have a $20\text{V}/\mu\text{s}$ slew rate.

7.4 Device Functional Modes

These devices are powered on when the supply is connected. This device can be operated as a single-supply operational amplifier or dual-supply amplifier depending on the application.

8 Applications and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくこととなります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

The TL08x series of operational amplifiers can be used in countless applications. The few applications in this section show principles used in all applications of these parts.

8.2 Typical Applications

8.2.1 Inverting Amplifier Application

A typical application for an operational amplifier in an inverting amplifier. This amplifier takes a positive voltage on the input, and makes it a negative voltage of the same magnitude. In the same manner, it also makes negative voltages positive.

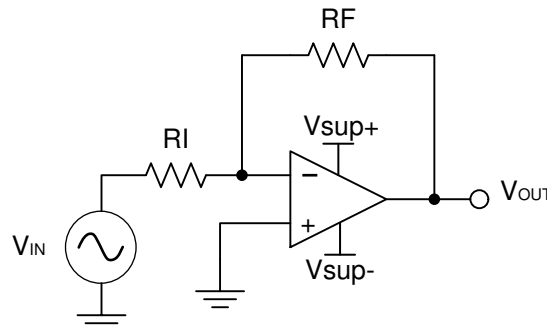


図 8-1. Schematic for Inverting Amplifier Application

8.2.1.1 Design Requirements

The supply voltage must be chosen such that it is larger than the input voltage range and output range. For instance, this application will scale a signal of $\pm 0.5\text{V}$ to $\pm 1.8\text{V}$. Setting the supply at $\pm 12\text{V}$ is sufficient to accommodate this application.

8.2.1.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier:

$$A_V = \frac{V_{OUT}}{V_{IN}} \quad (1)$$

$$A_V = \frac{1.8}{-0.5} = -3.6 \quad (2)$$

Once the desired gain is determined, choose a value for R_I or R_F . Choosing a value in the $\text{k}\Omega$ range is desirable because the amplifier circuit will use currents in the milliamp range. This causes the part will not draw too much current. This example will choose $10\text{k}\Omega$ for R_I which means $36\text{k}\Omega$ will be used for R_F . This was determined by Equation 3.

$$A_V = -\frac{R_F}{R_I} \quad (3)$$

8.2.1.3 Application Curve

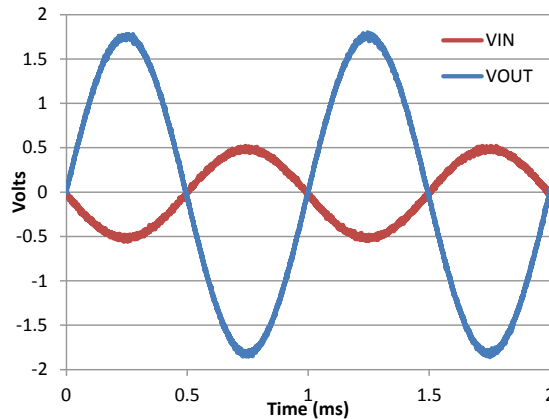


図 8-2. Input and Output Voltages of the Inverting Amplifier

8.3 System Examples

8.3.1 General Applications

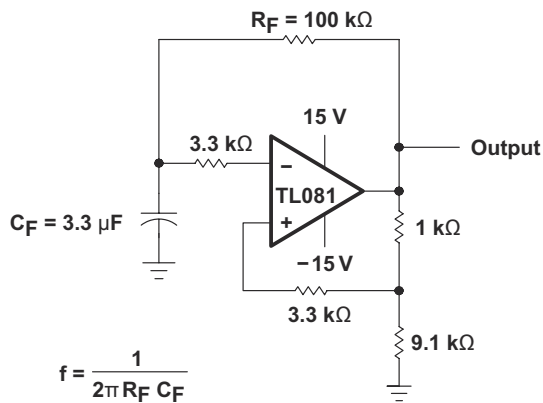


図 8-3. 0.5-Hz Square-Wave Oscillator

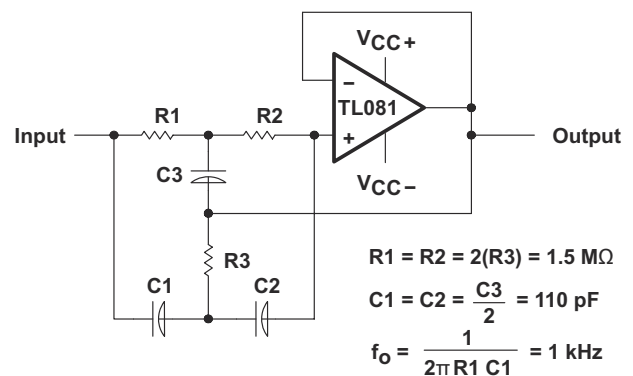


図 8-4. High-Q Notch Filter

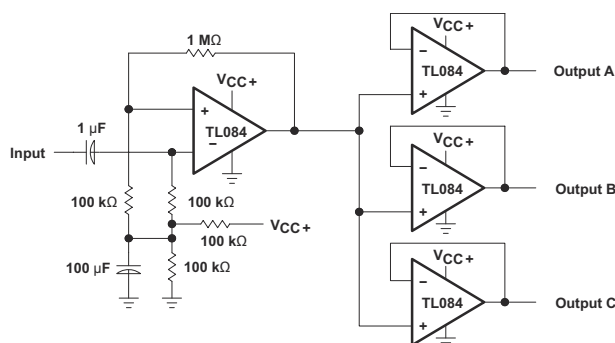
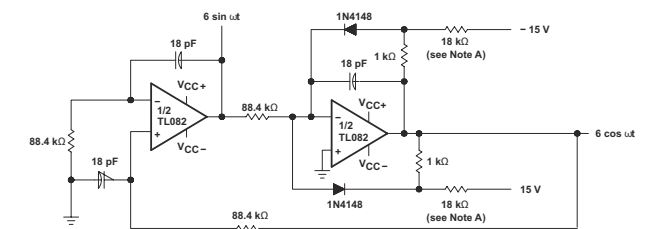


図 8-5. Audio-Distribution Amplifier



A. These resistor values may be adjusted for a symmetrical output.

図 8-6. 100-kHz Quadrature Oscillator

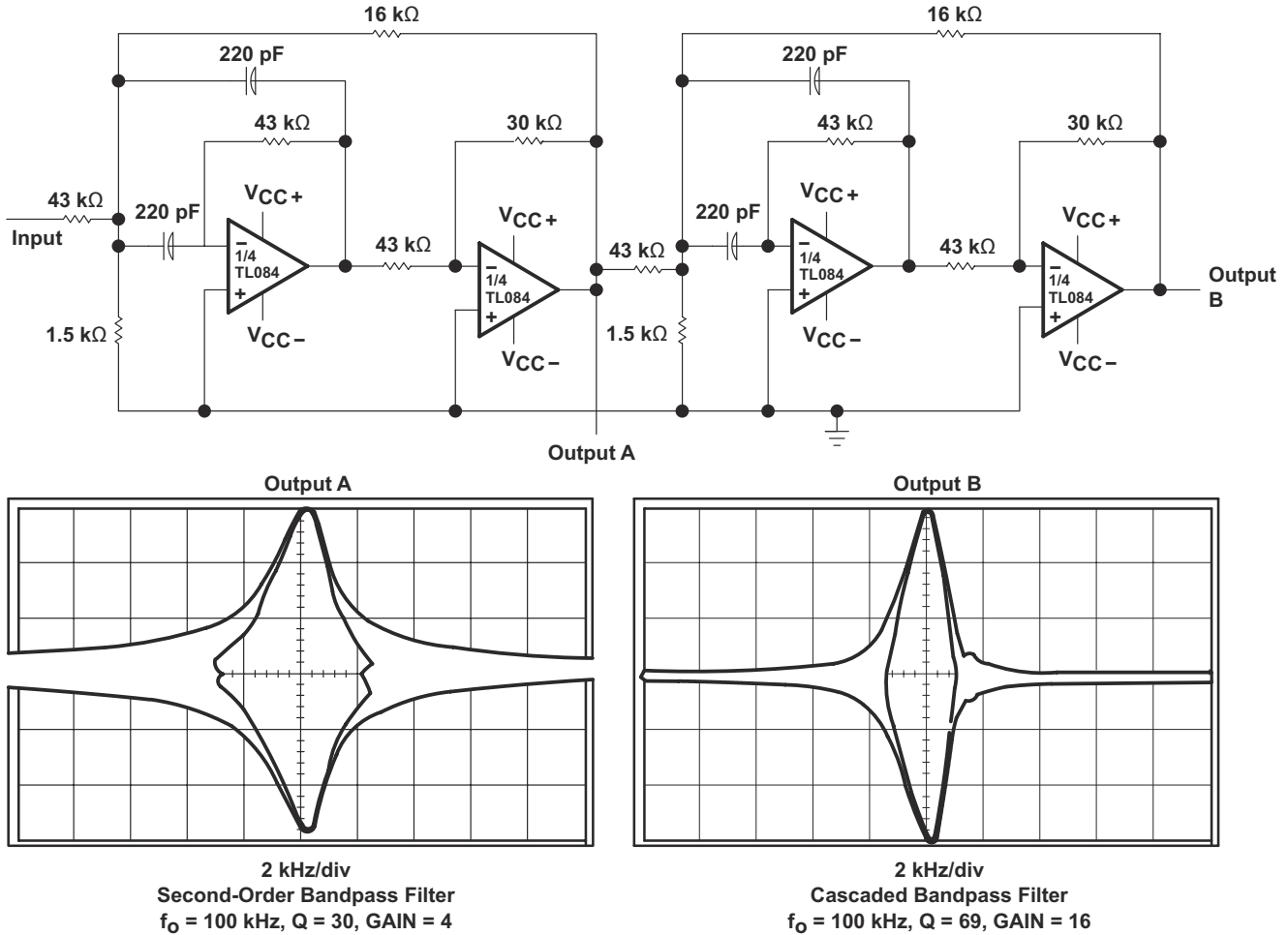


図 8-7. Positive-Feedback Bandpass Filter

8.4 Power Supply Recommendations

注意

Supply voltages larger than 36V for a single-supply or outside the range of $\pm 18\text{V}$ for a dual-supply can permanently damage the device (see [セクション 5.1](#)).

Place 0.1 μF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high impedance power supplies. For more detailed information on bypass capacitor placement, refer to [セクション 8.5](#).

8.5 Layout

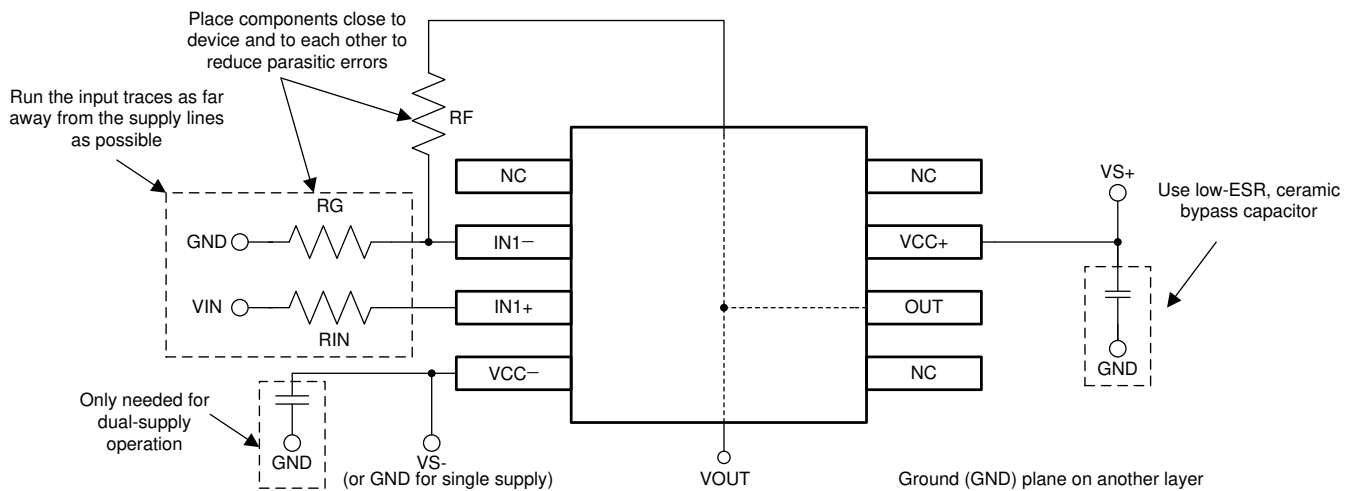
8.5.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

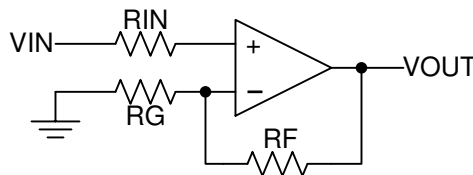
- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1 μF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.

- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Ensure to physically separate digital and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance, as shown in [セクション 8.5.2](#).
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

8.5.2 Layout Examples



☒ 8-8. Operational Amplifier Board Layout for Noninverting Configuration



☒ 8-9. Operational Amplifier Schematic for Noninverting Configuration

9 Device and Documentation Support

9.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

9.2 サポート・リソース

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9.5 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision M (December 2021) to Revision N (June 2024)	Page
• Changed Absolute Maximum Ratings, ESD Ratings, Recommended Operating Conditions, and Thermal Information sections by merging TL08xH and TL08xx specifications.....	9
• Changed Electrical Characteristics tables by merging TL08xC, TL08xAC, TL08xBC, TL08xI, and TL08xM specifications.....	14
• Increased gain bandwidth of all non-NS/non-PS packages and non-TL08xM devices from 3MHz to 5.25MHz.....	14
• Merged TL08xC, TL08xAC, TL08xBC, TL08xI, and TL08xM Switching Characteristics tables and renamed to Electrical Characteristics (AC).....	16
• Changed input voltage noise density at 1kHz for all non-PS/non-NS packages and all non-TL08xM devices to 37nV/√Hz.....	16
• Changed THD+N for all non-PS/non-NS packages and all non-TL08xM devices to 0.00012%.....	16
• Updated <i>Functional Block Diagram</i> and <i>Feature Description</i> sections.....	25
Changes from Revision L (July 2021) to Revision M (December 2021)	Page
• Corrected DCK pinout diagram and table in <i>Pin Configurations and Functions</i> section.....	3

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9851501Q2A	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9851501Q2A TL082MFKB	Samples
5962-9851501QPA	ACTIVE	CDIP	JG	8	50	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	9851501QPA TL082M	Samples
5962-9851503Q2A	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9851503Q2A TL084 MFKB	Samples
5962-9851503QCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9851503QC A TL084MJB	Samples
TL081ACD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI	0 to 70	081AC	
TL081ACDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	081AC	Samples
TL081ACP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL081ACP	Samples
TL081BCD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI	0 to 70	081BC	
TL081BCDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	081BC	Samples
TL081BCP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL081BCP	Samples
TL081CD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI	0 to 70	TL081C	
TL081CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL081C	Samples
TL081CP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL081CP	Samples
TL081CPE4	ACTIVE	PDIP	P	8	50	TBD	Call TI	Call TI	0 to 70		Samples
TL081CPSR	ACTIVE	SO	PS	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	T081	Samples
TL081HIDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	T81V	Samples
TL081HIDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	11P	Samples
TL081HIDR	ACTIVE	SOIC	D	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL081D	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TL081ID	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI	-40 to 85	TL081I	
TL081IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL081I	Samples
TL081IP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TL081IP	Samples
TL082ACD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI	0 to 70	082AC	
TL082ACDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC	Samples
TL082ACDRE4	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	0 to 70		Samples
TL082ACP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL082ACP	Samples
TL082ACPSR	ACTIVE	SO	PS	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082A	Samples
TL082BCD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI	0 to 70	082BC	
TL082BCDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC	Samples
TL082BCP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL082BCP	Samples
TL082BCPE4	ACTIVE	PDIP	P	8	50	TBD	Call TI	Call TI	0 to 70		Samples
TL082CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C	Samples
TL082CDRE4	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	0 to 70		Samples
TL082CDRG4	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	0 to 70		Samples
TL082CP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL082CP	Samples
TL082CPSR	ACTIVE	SO	PS	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Samples
TL082CPSRG4	ACTIVE	SO	PS	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Samples
TL082CPWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082	Samples
TL082CPWRG4	ACTIVE	TSSOP	PW	8	2000	TBD	Call TI	Call TI	0 to 70		Samples
TL082HIDDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	082F	Samples
TL082HIDR	ACTIVE	SOIC	D	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL082D	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TL082HIPWR	ACTIVE	TSSOP	PW	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	082HPW	Samples
TL082IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL082I	Samples
TL082IDRE4	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	-40 to 85		Samples
TL082IP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TL082IP	Samples
TL082IPE4	ACTIVE	PDIP	P	8	50	TBD	Call TI	Call TI	-40 to 85		Samples
TL082IPWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	Z082	Samples
TL082MFKB	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962- 9851501Q2A TL082MFKB	Samples
TL082MJG	ACTIVE	CDIP	JG	8	50	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	TL082MJG	Samples
TL082MJGB	ACTIVE	CDIP	JG	8	50	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	9851501QPA TL082M	Samples
TL084ACDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084AC	Samples
TL084ACN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL084ACN	Samples
TL084ACNSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084A	Samples
TL084BCDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC	Samples
TL084BCDRG4	ACTIVE	SOIC	D	14	2500	TBD	Call TI	Call TI	0 to 70		Samples
TL084BCN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL084BCN	Samples
TL084BCNE4	ACTIVE	PDIP	N	14	25	TBD	Call TI	Call TI	0 to 70		Samples
TL084CDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C	Samples
TL084CDRG4	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	0 to 70	TL084C	
TL084CN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	TL084CN	Samples
TL084CNSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TL084CPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	T084	Samples
TL084HIDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084HID	Samples
TL084HIDYYR	ACTIVE	SOT-23-THIN	DYY	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T084HDYY	Samples
TL084HIPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084PW	Samples
TL084ID	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	-40 to 85	TL084I	
TL084IDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I	Samples
TL084IDRE4	ACTIVE	SOIC	D	14	2500	TBD	Call TI	Call TI	-40 to 85		Samples
TL084IDRG4	ACTIVE	SOIC	D	14	2500	TBD	Call TI	Call TI	-40 to 85		Samples
TL084IN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TL084IN	Samples
TL084MFK	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	TL084MFK	Samples
TL084MFKB	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9851503Q2A TL084 MFKB	Samples
TL084MJ	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	TL084MJ	Samples
TL084MJB	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9851503QC A TL084MJB	Samples
TL084QDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q	Samples
TL084QDRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of ≤ 1000 ppm threshold. Antimony trioxide based flame retardants must also meet the ≤ 1000 ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TL082, TL082M, TL084, TL084M :

● Catalog : [TL082](#), [TL084](#)

● Automotive : [TL082-Q1](#), [TL082-Q1](#)

● Military : [TL082M](#), [TL084M](#)

NOTE: Qualified Version Definitions:

● Catalog - TI's standard catalog product

● Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TL081ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081CPSR	SO	PS	8	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
TL081HIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TL081HIDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TL081HIDR	SOIC	D	8	3000	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL081IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082ACPSR	SO	PS	8	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TL082BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082CPSR	SO	PS	8	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
TL082CPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TL082CPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TL082HIDDFR	SOT-23-THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TL082HIDR	SOIC	D	8	3000	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082HIPWR	TSSOP	PW	8	3000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TL082IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL082IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TL082IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TL084ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084ACNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TL084BCDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084BCDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TL084CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TL084CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TL084HIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084HIDYYR	SOT-23-THIN	DYY	14	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
TL084HIPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TL084IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084QDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TL084QDRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

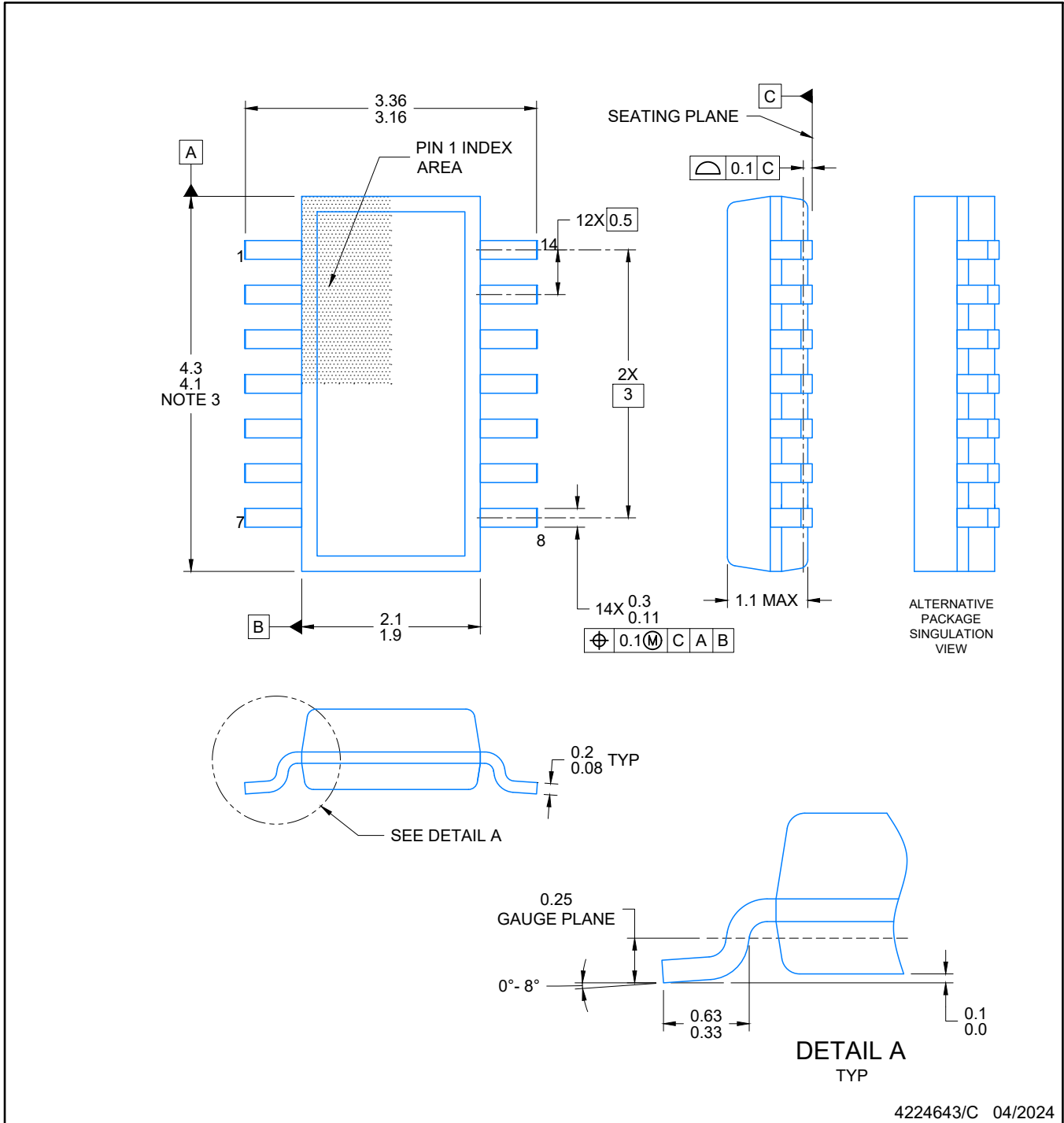
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TL081ACDR	SOIC	D	8	2500	356.0	356.0	35.0
TL081ACDR	SOIC	D	8	2500	340.5	338.1	20.6
TL081BCDR	SOIC	D	8	2500	340.5	338.1	20.6
TL081BCDR	SOIC	D	8	2500	356.0	356.0	35.0
TL081CDR	SOIC	D	8	2500	340.5	338.1	20.6
TL081CDR	SOIC	D	8	2500	356.0	356.0	35.0
TL081CPSR	SO	PS	8	2000	356.0	356.0	35.0
TL081HIDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TL081HIDCKR	SC70	DCK	5	3000	190.0	190.0	30.0
TL081HIDR	SOIC	D	8	3000	356.0	356.0	35.0
TL081IDR	SOIC	D	8	2500	356.0	356.0	35.0
TL081IDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082ACDR	SOIC	D	8	2500	356.0	356.0	35.0
TL082ACDR	SOIC	D	8	2500	356.0	356.0	35.0
TL082ACDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082ACPSR	SO	PS	8	2000	356.0	356.0	35.0
TL082BCDR	SOIC	D	8	2500	356.0	356.0	35.0
TL082BCDR	SOIC	D	8	2500	340.5	338.1	20.6

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TL082CDR	SOIC	D	8	2500	356.0	356.0	35.0
TL082CDR	SOIC	D	8	2500	356.0	356.0	35.0
TL082CDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082CPSR	SO	PS	8	2000	356.0	356.0	35.0
TL082CPWR	TSSOP	PW	8	2000	356.0	356.0	35.0
TL082CPWR	TSSOP	PW	8	2000	356.0	356.0	35.0
TL082HIDDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
TL082HIDR	SOIC	D	8	3000	356.0	356.0	35.0
TL082HIPWR	TSSOP	PW	8	3000	356.0	356.0	35.0
TL082IDR	SOIC	D	8	2500	356.0	356.0	35.0
TL082IDR	SOIC	D	8	2500	356.0	356.0	35.0
TL082IDR	SOIC	D	8	2500	340.5	338.1	20.6
TL082IPWR	TSSOP	PW	8	2000	356.0	356.0	35.0
TL082IPWR	TSSOP	PW	8	2000	356.0	356.0	35.0
TL084ACDR	SOIC	D	14	2500	333.2	345.9	28.6
TL084ACNSR	SO	NS	14	2000	356.0	356.0	35.0
TL084BCDR	SOIC	D	14	2500	356.0	356.0	35.0
TL084BCDR	SOIC	D	14	2500	333.2	345.9	28.6
TL084CDR	SOIC	D	14	2500	356.0	356.0	35.0
TL084CDR	SOIC	D	14	2500	356.0	356.0	35.0
TL084CDR	SOIC	D	14	2500	333.2	345.9	28.6
TL084CNSR	SO	NS	14	2000	356.0	356.0	35.0
TL084CPWR	TSSOP	PW	14	2000	356.0	356.0	35.0
TL084CPWR	TSSOP	PW	14	2000	356.0	356.0	35.0
TL084HIDR	SOIC	D	14	2500	356.0	356.0	35.0
TL084HIDYYR	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8
TL084HIPWR	TSSOP	PW	14	2000	356.0	356.0	35.0
TL084IDR	SOIC	D	14	2500	333.2	345.9	28.6
TL084IDR	SOIC	D	14	2500	356.0	356.0	35.0
TL084QDR	SOIC	D	14	2500	356.0	356.0	35.0
TL084QDRG4	SOIC	D	14	2500	350.0	350.0	43.0

TUBE


*All dimensions are nominal

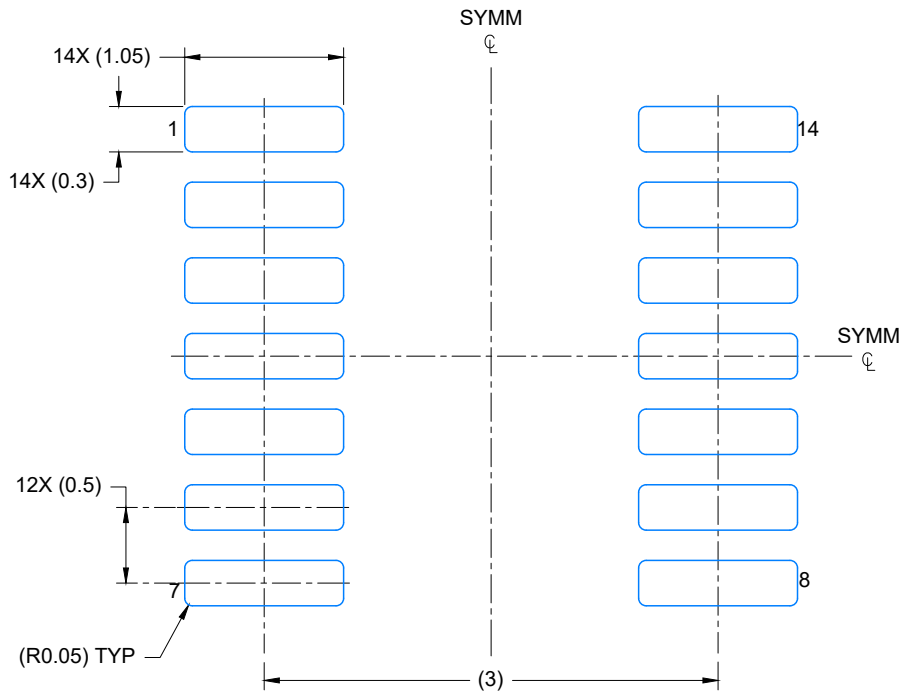
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
5962-9851501Q2A	FK	LCCC	20	55	506.98	12.06	2030	NA
5962-9851503Q2A	FK	LCCC	20	55	506.98	12.06	2030	NA
TL081ACP	P	PDIP	8	50	506	13.97	11230	4.32
TL081BCP	P	PDIP	8	50	506	13.97	11230	4.32
TL081CP	P	PDIP	8	50	506	13.97	11230	4.32
TL081IP	P	PDIP	8	50	506	13.97	11230	4.32
TL082ACP	P	PDIP	8	50	506	13.97	11230	4.32
TL082BCP	P	PDIP	8	50	506	13.97	11230	4.32
TL082CP	P	PDIP	8	50	506	13.97	11230	4.32
TL082IP	P	PDIP	8	50	506	13.97	11230	4.32
TL082MFKB	FK	LCCC	20	55	506.98	12.06	2030	NA
TL084ACN	N	PDIP	14	25	506	13.97	11230	4.32
TL084ACN	N	PDIP	14	25	506	13.97	11230	4.32
TL084ACN	N	PDIP	14	25	506	13.97	11230	4.32
TL084BCN	N	PDIP	14	25	506	13.97	11230	4.32
TL084BCN	N	PDIP	14	25	506	13.97	11230	4.32
TL084BCN	N	PDIP	14	25	506	13.97	11230	4.32
TL084CN	N	PDIP	14	25	506	13.97	11230	4.32
TL084CN	N	PDIP	14	25	506	13.97	11230	4.32
TL084CNE4	N	PDIP	14	25	506	13.97	11230	4.32
TL084CNE4	N	PDIP	14	25	506	13.97	11230	4.32
TL084IN	N	PDIP	14	25	506	13.97	11230	4.32
TL084IN	N	PDIP	14	25	506	13.97	11230	4.32
TL084IN	N	PDIP	14	25	506	13.97	11230	4.32
TL084INE4	N	PDIP	14	25	506	13.97	11230	4.32
TL084INE4	N	PDIP	14	25	506	13.97	11230	4.32
TL084INE4	N	PDIP	14	25	506	13.97	11230	4.32
TL084INE4	N	PDIP	14	25	506	13.97	11230	4.32
TL084MFK	FK	LCCC	20	55	506.98	12.06	2030	NA
TL084MFKB	FK	LCCC	20	55	506.98	12.06	2030	NA



4224643/C 04/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AB



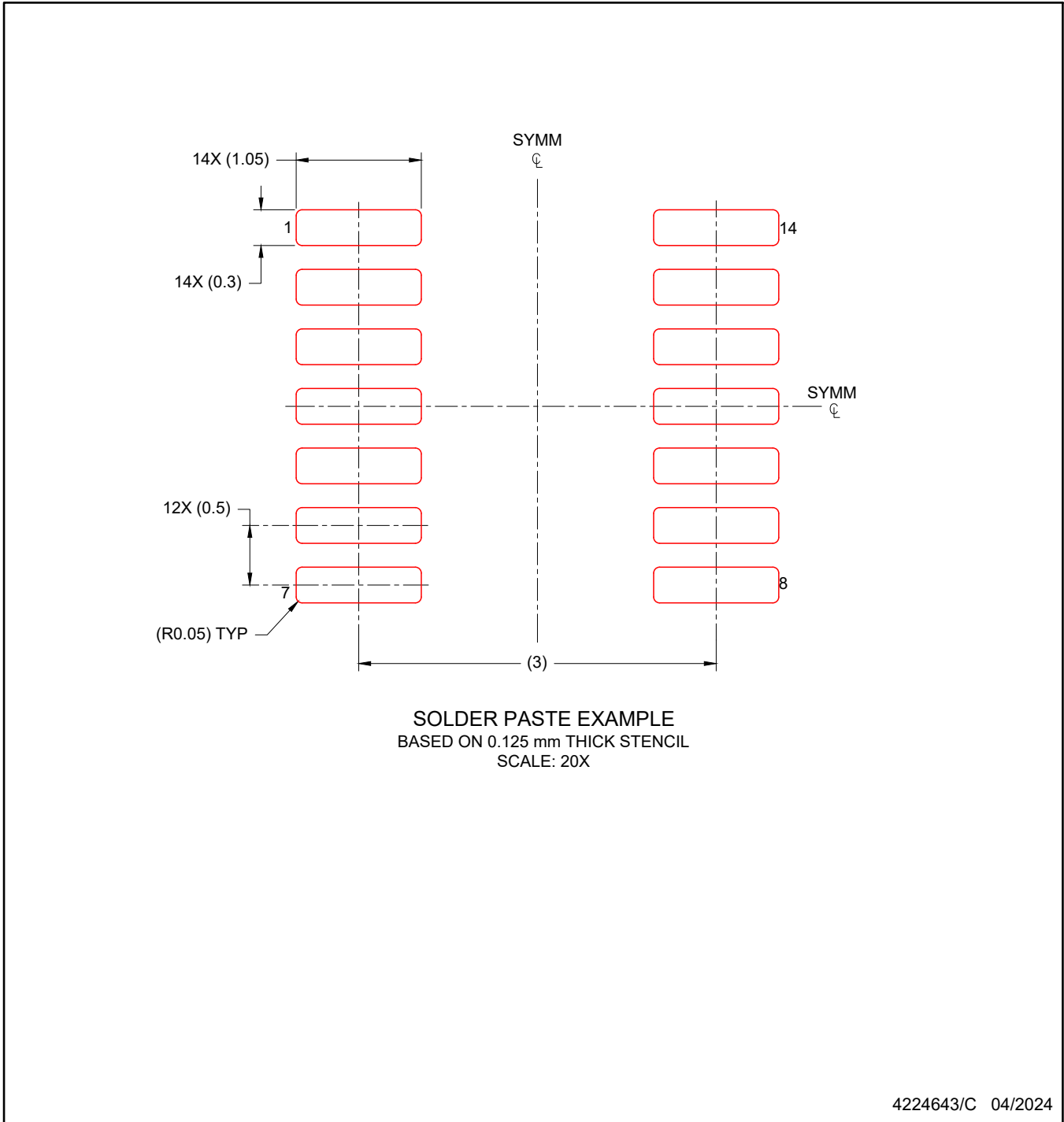
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224643/C 04/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

MECHANICAL DATA

NS (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

GENERIC PACKAGE VIEW

FK 20

LCCC - 2.03 mm max height

8.89 x 8.89, 1.27 mm pitch

LEADLESS CERAMIC CHIP CARRIER

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4229370VA\

J 14

GENERIC PACKAGE VIEW
CDIP - 5.08 mm max height
CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4040083-5/G

J0014A



PACKAGE OUTLINE

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



4214771/A 05/2017

NOTES:

1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package is hermetically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
5. Falls within MIL-STD-1835 and GDIP1-T14.

EXAMPLE BOARD LAYOUT

J0014A

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE: 5X



4214771/A 05/2017

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

DDF0008A



PACKAGE OUTLINE

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



4222047/E 07/2024

NOTES:

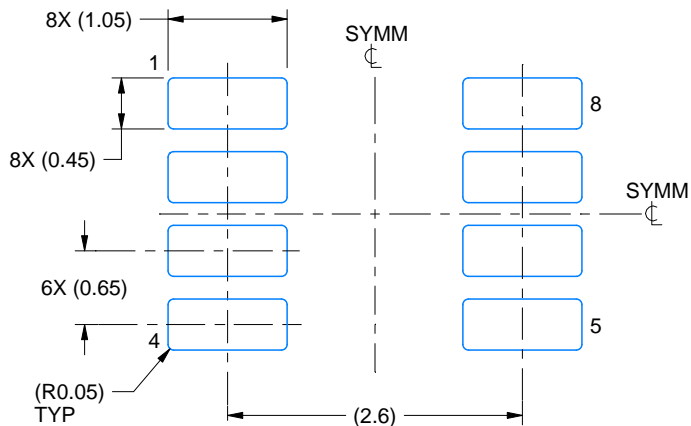
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

EXAMPLE BOARD LAYOUT

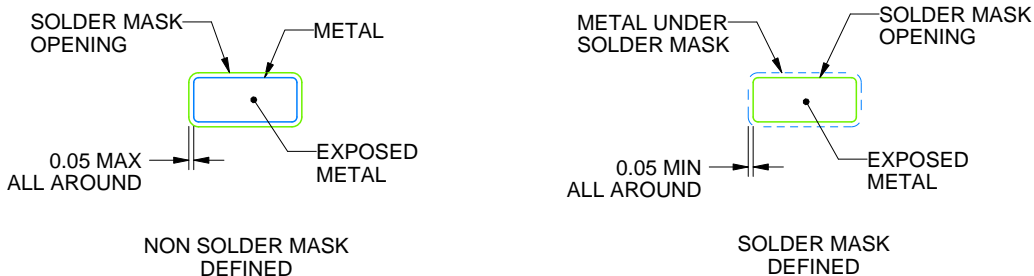
DDF0008A

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4222047/E 07/2024

NOTES: (continued)

- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DDF0008A

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4222047/E 07/2024

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.



D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

- Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed $.006$ [0.15] per side.
- This dimension does not include interlead flash.
- Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
 EXPOSED METAL SHOWN
 SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

MECHANICAL DATA

PS (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

PS (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

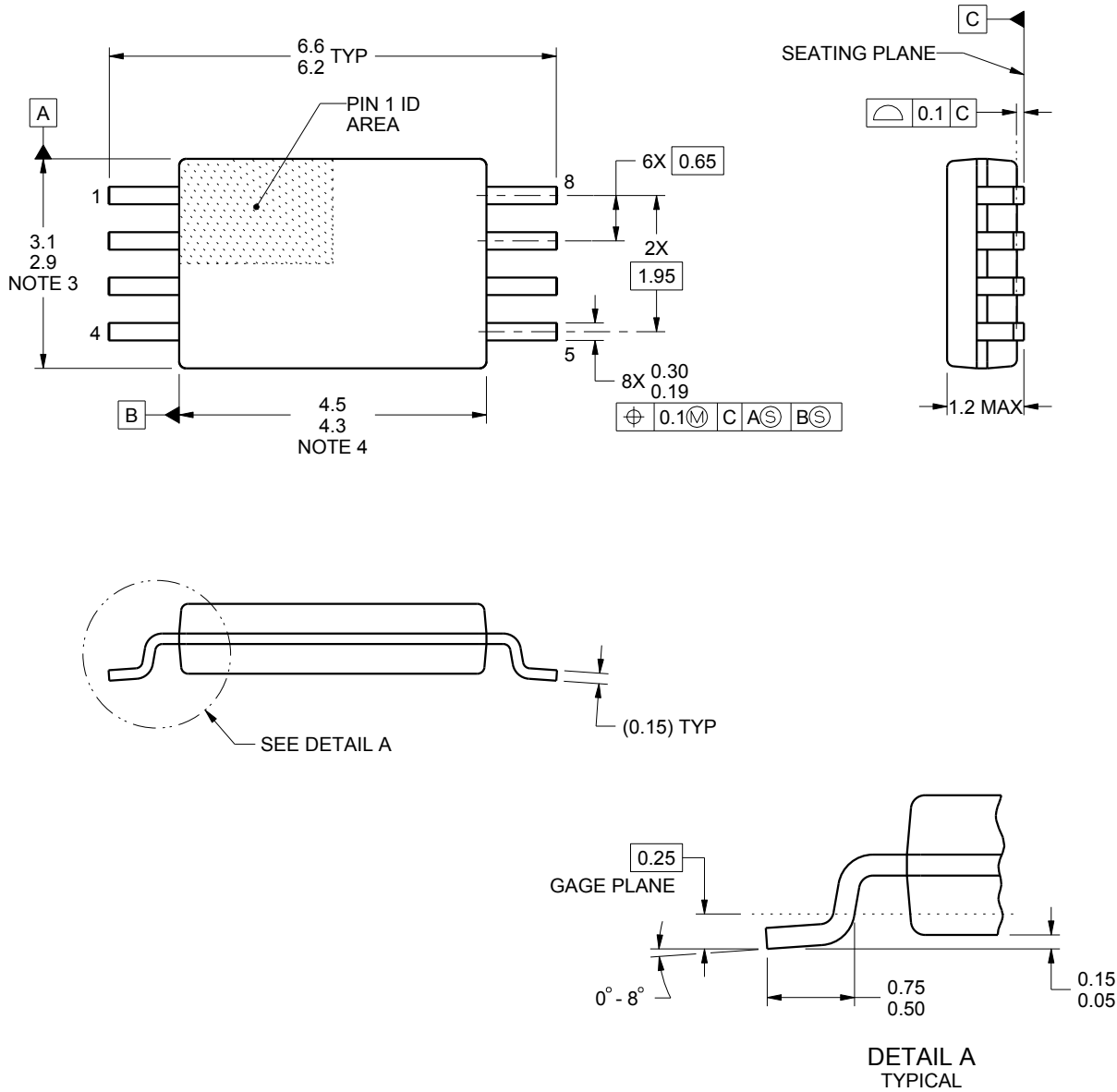
PW0008A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4221848/A 02/2015

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153, variation AA.

EXAMPLE BOARD LAYOUT

PW0008A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
SCALE:10X



SOLDER MASK DETAILS
NOT TO SCALE

4221848/A 02/2015

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0008A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:10X

4221848/A 02/2015

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

JG0008A

CDIP - 5.08 mm max height

CERAMIC DUAL IN-LINE PACKAGE



NOTES:

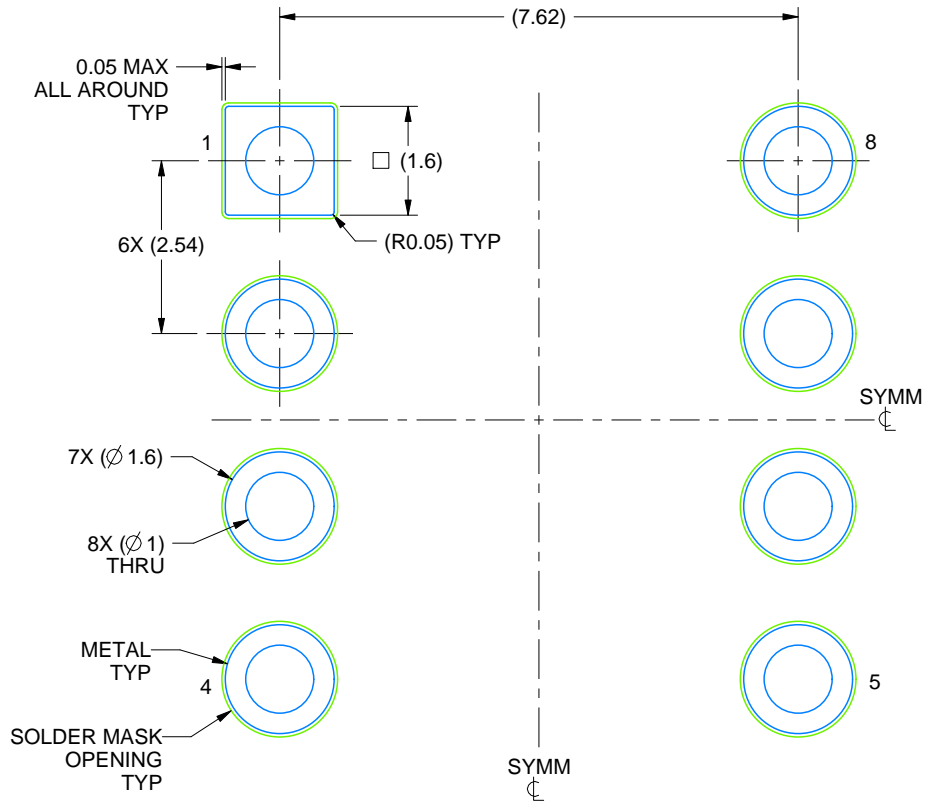
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package can be hermetically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification.
5. Falls within MIL STD 1835 GDIP1-T8

EXAMPLE BOARD LAYOUT

JG0008A

CDIP - 5.08 mm max height

CERAMIC DUAL IN-LINE PACKAGE



LAND PATTERN EXAMPLE
NON SOLDER MASK DEFINED
SCALE: 9X

4230036/A 09/2023

EXAMPLE BOARD LAYOUT

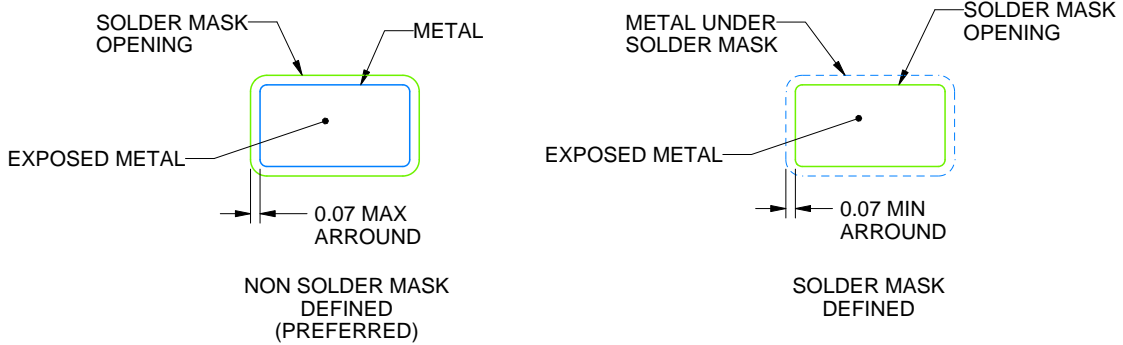
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

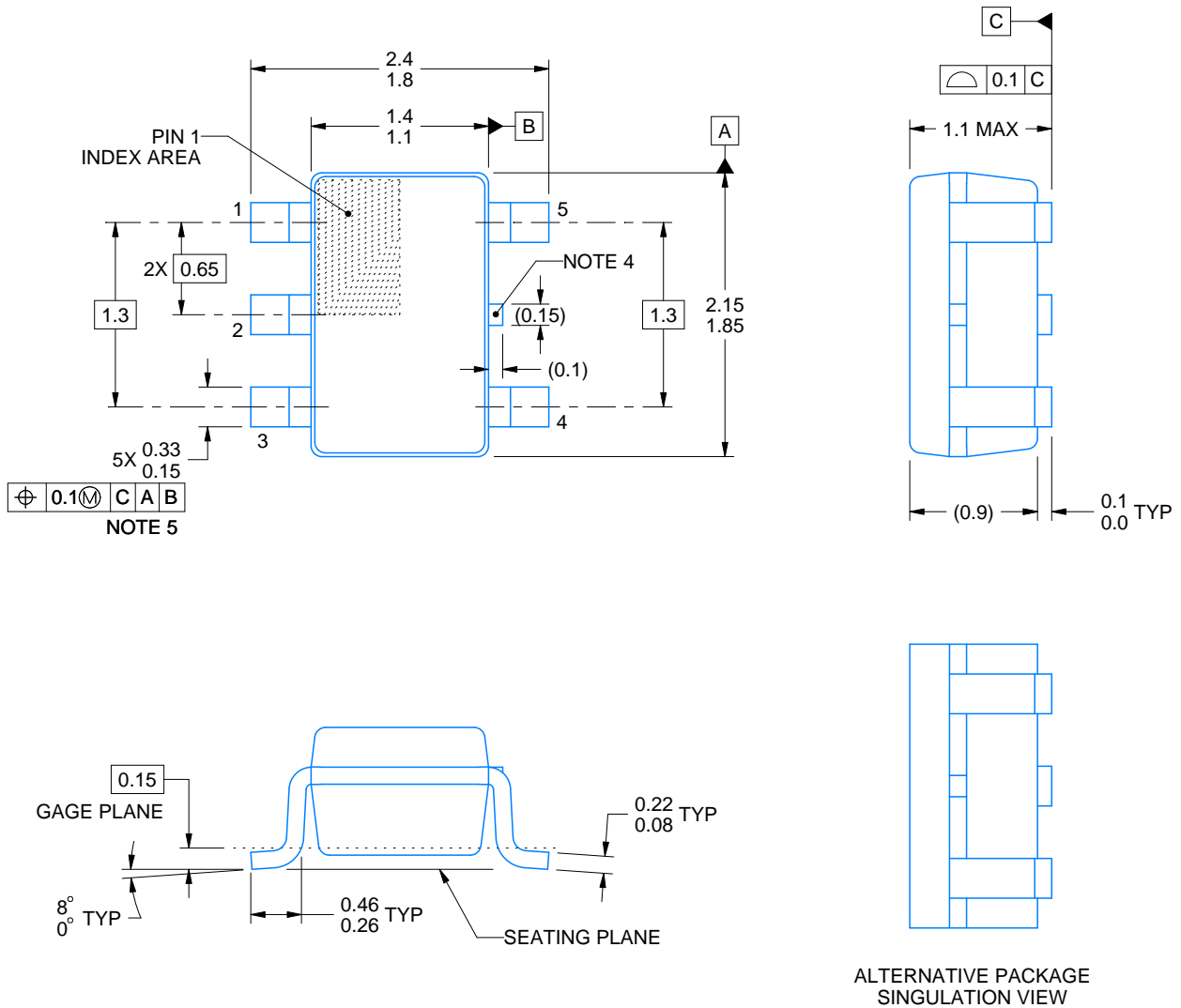
DCK0005A



PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/E 06/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214834/E 06/2024

NOTES: (continued)

- 7. Publication IPC-7351 may have alternate designs.
- 8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/E 06/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

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